

ISOFACE™ digital isolators 2DIBx40xF

Basic dual-channel digital isolators qualified for industrial applications

Description

The ISOFACE™ 2DIBx40xF dual-channel digital isolator family supports data rates of up to 40 Mbps and ensures robust data communication over a wide ambient operating temperature range (-40°C to +125°C) and across production spread. Infineon's robust Coreless Transformer (CT) technology ensures high immunity against system noise (CMTI of min. 100 kV/μs) and withstands up to 3000 V_{rms} isolation voltage (V_{ISO}). Two data channels in a PG-DSO-8 narrow-body 150-mil package allow simplified designs with high power density and improve system efficiency with low power consumption. Product variants with different channel configurations and fail-safe default output states are available.

Features

- Data rates up to 40 Mbps
- Wide operating supply voltage 2.7 V to 6.5 V
- Low current consumption (max. 1.65 mA/ch @ 1 Mbps, 3.3 V, 15 pF)
- High CMTI: 100 kV/μs (min)
- Propagation delay: 26 ns (typ) with 3 ns (max) channel-to-channel mismatch
- Maximum pulse width distortion of 3 ns
- Fail-safe default output high (2DIBx401F) or low (2DIBx400F) options
- Variable input thresholds (CMOS)
- Wide ambient operating temperature range (-40°C to +125°C)
- RoHS-compliant PG-DSO-8 narrow-body 150-mil package



Potential applications

- Server, telecom and industrial Switch-Mode Power Supplies (SMPS)
- Industrial automation systems
- Motor drives
- Medical equipment
- Solar inverters

Product validation

Fully qualified according to JEDEC for industrial applications.

Isolation and safety certificates

- UL1577 (Ed. 5) with V_{ISO} = 3000 V_{rms} (certification n. E311313)
- VDE 0884-17 and IEC 60747-17 ¹⁾ with V_{IOTM} = 4242 V_{pk}, V_{IORM} = 1000 V_{pk}, V_{IOSM} = 6000 V_{pk} ²⁾
- EN and CQC certification for IEC 62368-1, IEC 60601-1, IEC 61010-1 and GB4943.1 system standards²⁾

¹ IEC 60747-17 and its German equivalent VDE 0884-17 is the successor of the component standard VDE 0884-11, which will expire in 2023

² Certification planned

ISOFACE™ digital isolators 2DIBx40xF
Basic dual-channel digital isolators qualified for industrial applications



ISOFACE™ 2DIBx40xF product portfolio

ISOFACE™ 2DIBx40xF product portfolio

Part number	Channel configuration	Default output state	Input threshold	Isolation rating	Package
2DIB0400F	2 forward 0 reverse (2+0)	Low	Variable (CMOS)	$V_{ISO} = 3000 V_{rms}$ (UL1577 Ed. 5)	PG-DSO-8 narrow-body 150 mil 5 x 6 mm
2DIB0401F		High			
2DIB1400F	1 forward 1 reverse (1+1)	Low			
2DIB1401F		High			

Table of contents

	Description	1
	Features	1
	Potential applications	1
	Product validation	1
	Isolation and safety certificates	1
	ISOFACE™ 2DIBx40xF product portfolio	2
	Table of contents	3
1	Functional block diagram	5
2	Pin configuration	6
3	Functional description	8
3.1	Truth tables	8
3.2	Timing diagrams	8
3.3	Data transmission input-to-output	10
3.4	Input/output voltage levels description	10
3.5	Supply characteristics	11
4	Thermal and electrical characteristics	13
4.1	Absolute maximum ratings	13
4.2	Additional ESD ratings	13
4.3	Thermal characteristics	14
4.4	Operating range	16
4.5	Common-mode transient immunity (CMTI)	16
4.6	Power supply - UVLO	16
4.7	Electrical characteristics	17
4.7.1	Electrical characteristics - 6.5 V supply	17
4.7.1.1	Logic inputs	17
4.7.1.2	Logic outputs	17
4.7.1.3	Power supply - 2DIB040xF (2+0)	18
4.7.1.4	Power supply - 2DIB140xF (1+1)	19
4.7.1.5	Dynamic characteristics	20
4.7.2	Electrical characteristics - 5 V supply	21
4.7.2.1	Logic inputs	21
4.7.2.2	Logic outputs	21
4.7.2.3	Power supply - 2DIB040xF (2+0)	22
4.7.2.4	Power supply - 2DIB140xF (1+1)	23
4.7.2.5	Dynamic characteristics	24
4.7.3	Electrical characteristics - 3.3 V supply	25
4.7.3.1	Logic inputs	25

Table of contents

4.7.3.2	Logic outputs	25
4.7.3.3	Power supply - 2DIB040xF (2+0)	26
4.7.3.4	Power supply - 2DIB140xF (1+1)	27
4.7.3.5	Dynamic characteristics	28
4.7.4	Electrical characteristics - 2.7 V supply	29
4.7.4.1	Logic inputs	29
4.7.4.2	Logic outputs	29
4.7.4.3	Power supply - 2DIB040xF (2+0)	30
4.7.4.4	Power supply - 2DIB140xF (1+1)	31
4.7.4.5	Dynamic characteristics	32
4.8	Insulation and safety-related specifications	33
4.8.1	Insulation characteristics	33
4.8.2	Safety-limiting values	35
4.8.2.1	Thermal derating curve	35
5	Application and Implementation	36
5.1	Detailed Description	36
5.2	Application examples	37
5.2.1	Isolating gate drive control signals	37
5.2.2	Isolating communication interfaces	38
6	Package dimensions	39
7	Ordering guide	42
8	Revision history	43
	Disclaimer	44

1 Functional block diagram

1 Functional block diagram

Figure 1 and Figure 2 illustrate the internal block diagram of the ISOFACE™ 2DIB040xF (2+0 channel configuration) and 2DIB140xF (1+1 channel configuration), respectively.

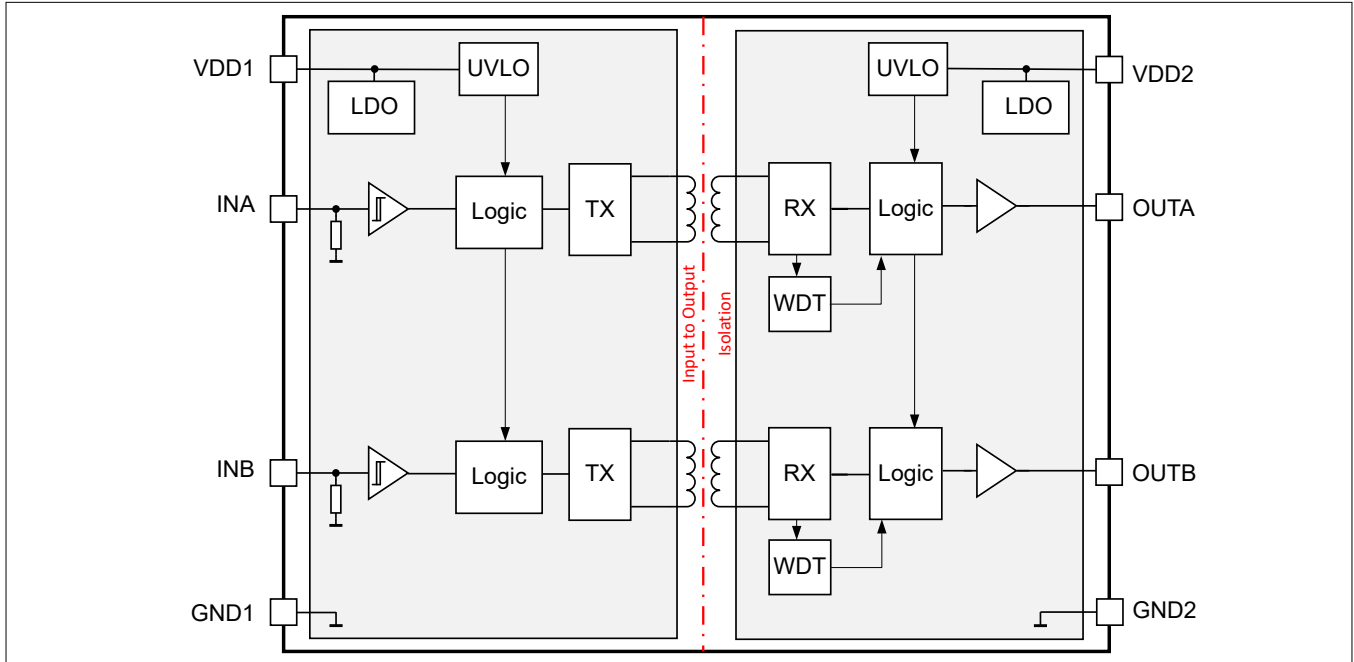


Figure 1 ISOFACE™ 2DIB040xF (2+0 channel configuration)

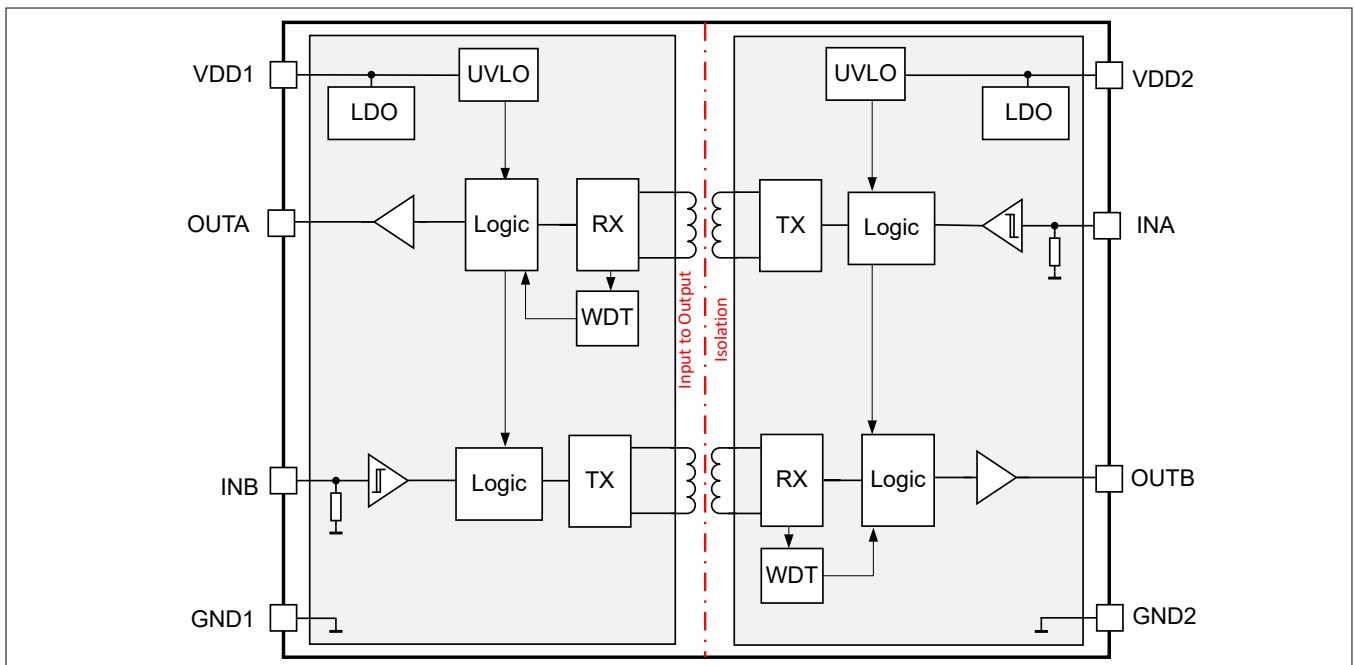


Figure 2 ISOFACE™ 2DIB140xF (1+1 channel configuration)

2 Pin configuration

2 Pin configuration

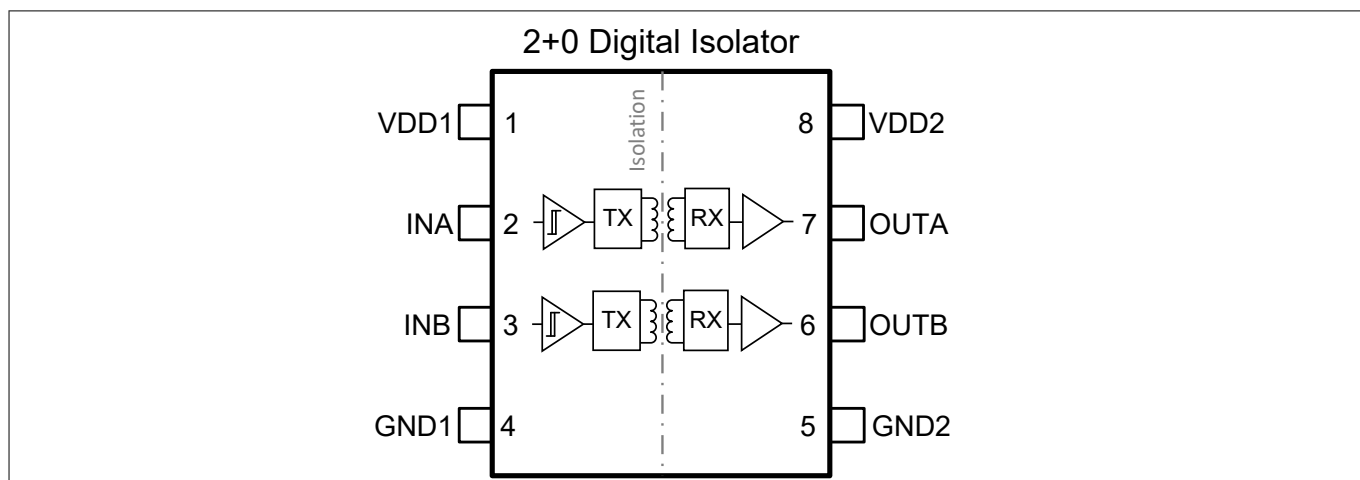


Figure 3 Pin-out for ISOFACE™ 2DIB040xF

Table 1 Pin definitions and functions for ISOFACE™ 2DIB040xF

Name	Pin	Type	Function
VDD1	1	I	Positive supply voltage 1
INA	2	I	Channel A input
INB	3	I	Channel B input
GND1	4	-	Ground 1
GND2	5	-	Ground 2
OUTB	6	O	Channel B output
OUTA	7	O	Channel A output
VDD2	8	I	Positive supply voltage 2

2 Pin configuration

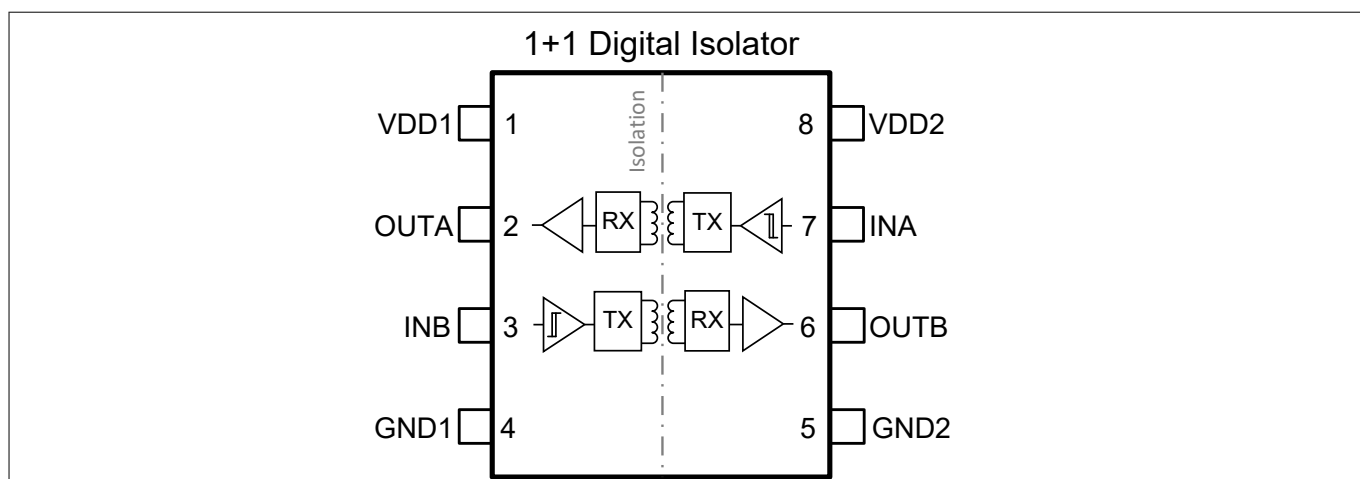


Figure 4 Pin-out for ISOFACE™ 2DIB140xF

Table 2 Pin definitions and functions for ISOFACE™ 2DIB140xF

Name	Pin	Type	Function
VDD1	1	I	Positive supply voltage 1
OUTA	2	O	Channel A output
INB	3	I	Channel B input
GND1	4	-	Ground 1
GND2	5	-	Ground 2
OUTB	6	O	Channel B output
INA	7	I	Channel A input
VDD2	8	I	Positive supply voltage 2

3 Functional description

3 Functional description

This chapter provides a summary of the integrated functions and features, and describes the relationships between them. The parameters and equations are based on typical values at $T_A = 25\text{ °C}$.

3.1 Truth tables

Table 3 Truth table for 2-channel Digital Isolator

$V_{DDI}^{1)}$	$V_{DDO}^{1)}$	V_{INX}	V_{OUTX}
Powered	Powered	H ²⁾	H
		L ²⁾	L
Unpowered	Powered	X ²⁾	Default ³⁾
X	Unpowered	X	Z ²⁾

- 1) V_{DDI} and V_{DDO} refer to the supply voltages on the input and output sides of a given channel, respectively
- 2) H means "high" and L means "low", X means "irrelevant", Z means "high-impedance"
- 3) Refer to product variants in [Ordering guide](#)

3.2 Timing diagrams

Figure 5 illustrates the test set-up for the electrical characteristics described in [Electrical characteristics](#).

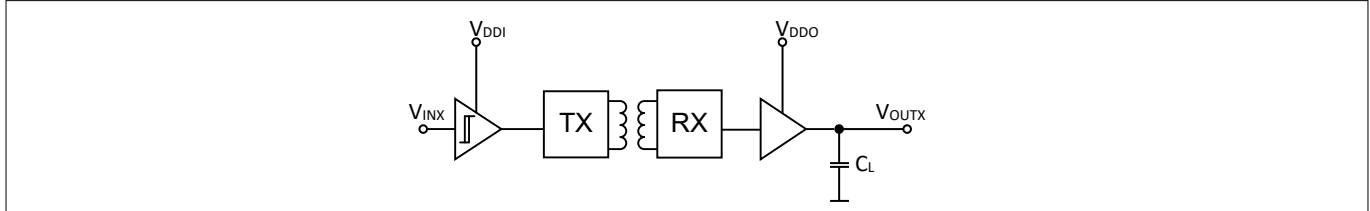


Figure 5 Test circuit

Figure 6 illustrates the input-to-output propagation delays as observed at the capacitively loaded output.

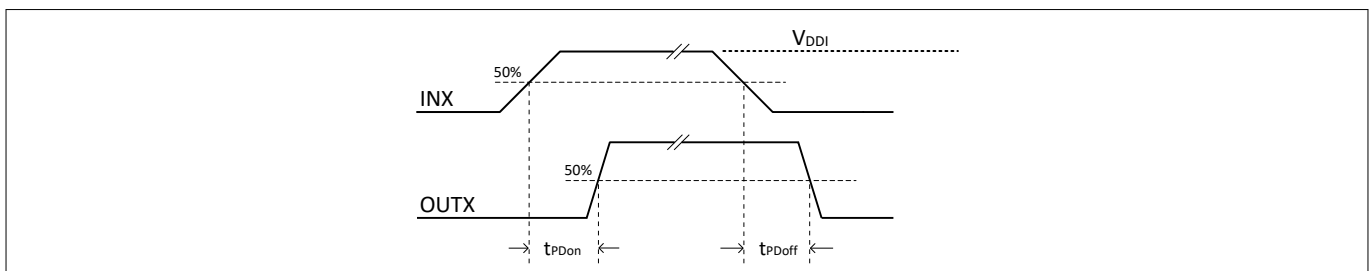


Figure 6 Propagation delays

3 Functional description

Figure 7 illustrates the rise and fall times as observed at the capacitively loaded output.

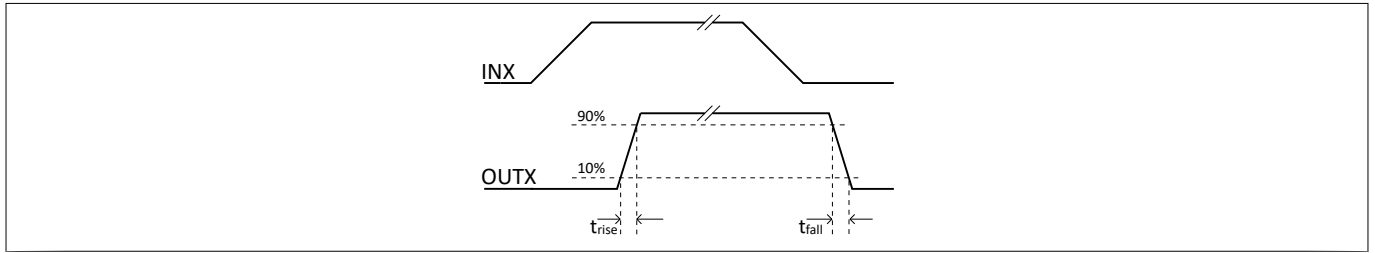


Figure 7 Rise, fall times

Figure 8 illustrates the output behavior to supply UVLO events when $V_{DD1/2}$ crosses the UVLO thresholds during rising or falling transitions (power-up, power-down, supply noise). Note that the input (V_{DD1}) and output (V_{DD2}) supplies are rising and falling at the same time.

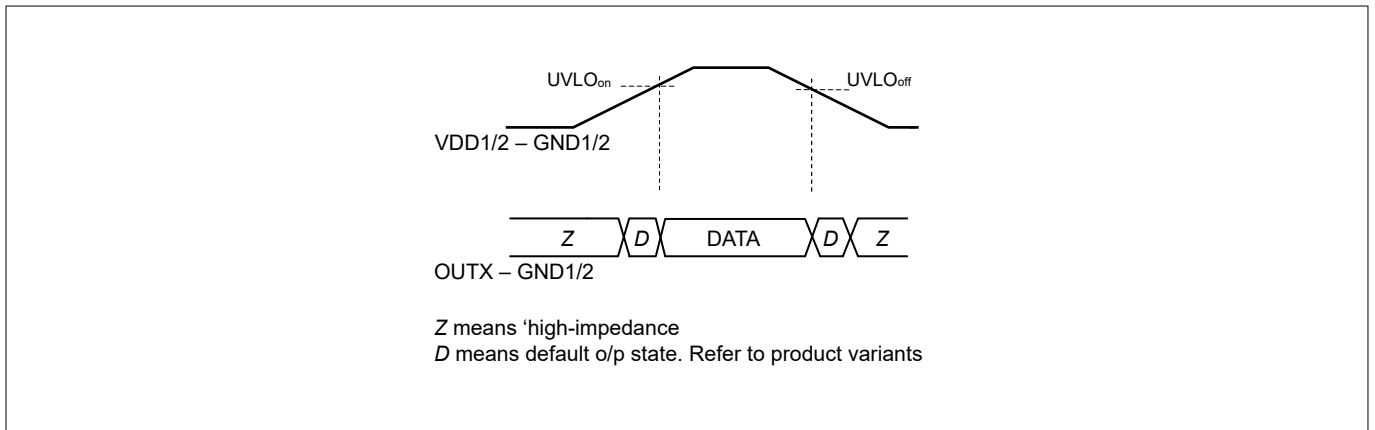


Figure 8 Under-voltage lockout

Figure 9 illustrates the time taken for the output to reach the default value when the power supply of the input channel goes below the UVLOoff value.

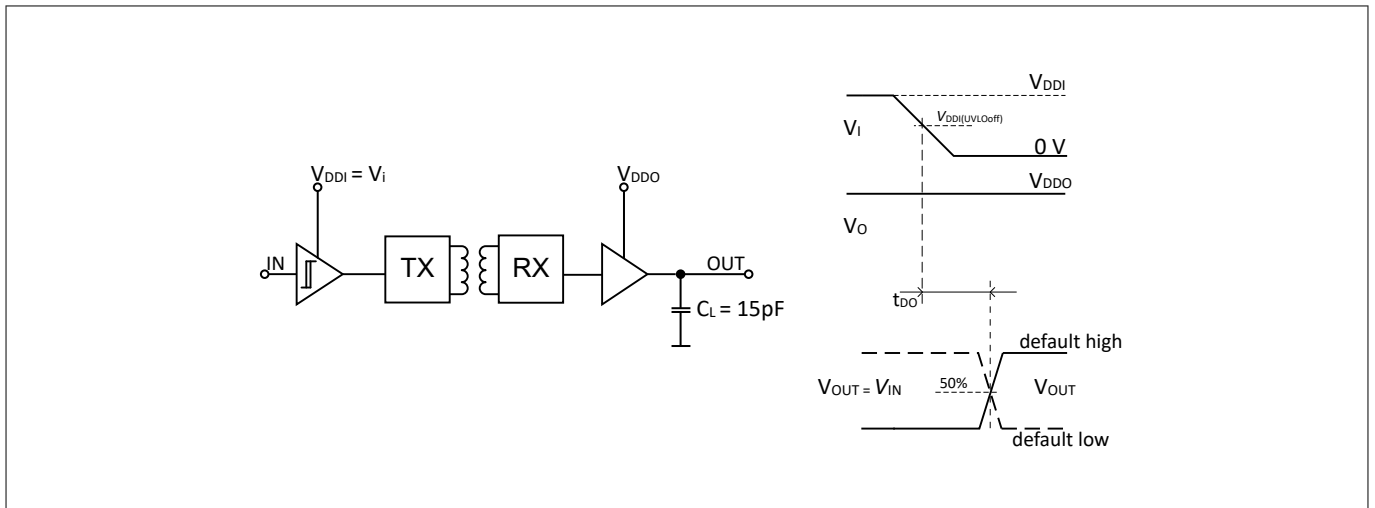


Figure 9 Default output delay time

3 Functional description

Figure 10 illustrates the time taken for the output to follow the input when the power supplies of the input and output sides of the digital isolator have different start-up timings. The power-up time is $t_{PU} = \max\{t_{PU1}, t_{PU2}\}$.

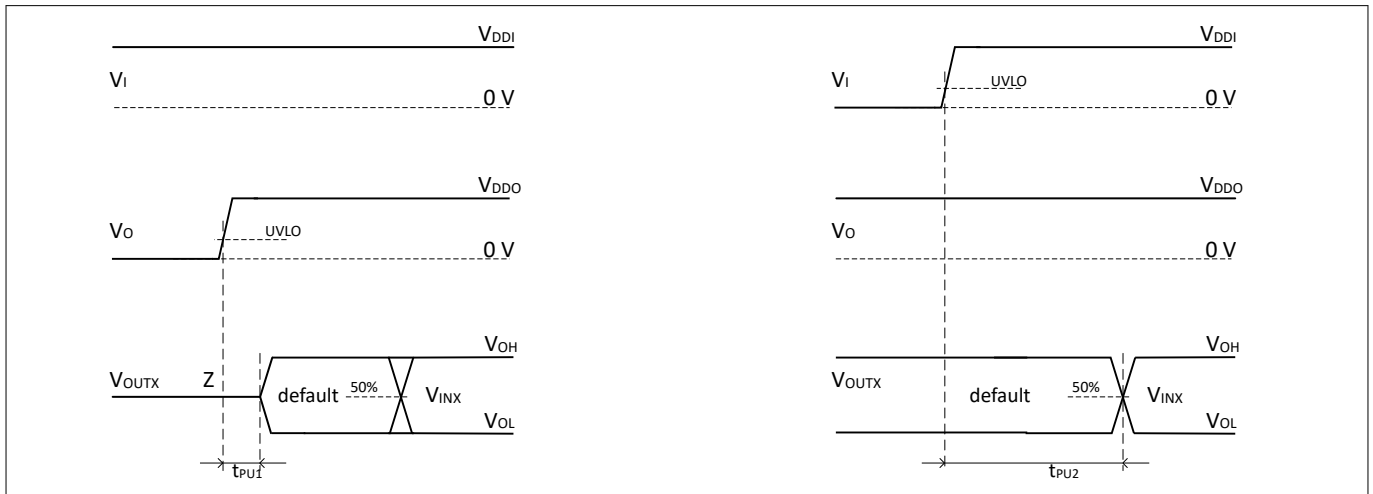


Figure 10 Power-up delay time

3.3 Data transmission input-to-output

Communication based on Coreless Transformer (CT) is used for signal transfer between input and output channels. If a constant DC level within the operating range is applied at the input, a proven high resolution pulse repetition scheme ensure functionality, enabling the output to follow the constant DC input. It also enables recovery from communication fails and safe system shutdown. In case of a power loss at the input channel, the pulse repetition scheme will be disabled and a watch-dog timer at the output triggers approximately after t_{D0} time period and drives the channel output to the default state. In case of multiple channels on the output side, the first watch-dog timer detecting the power loss at the input will drive all output channels on that side to default value. Once the power supply on the input channels is above the threshold value ($V_{DDX(UVLOon)}$), the communication is restored and the output will follow the input as shown in Figure 10.

3.4 Input/output voltage levels description

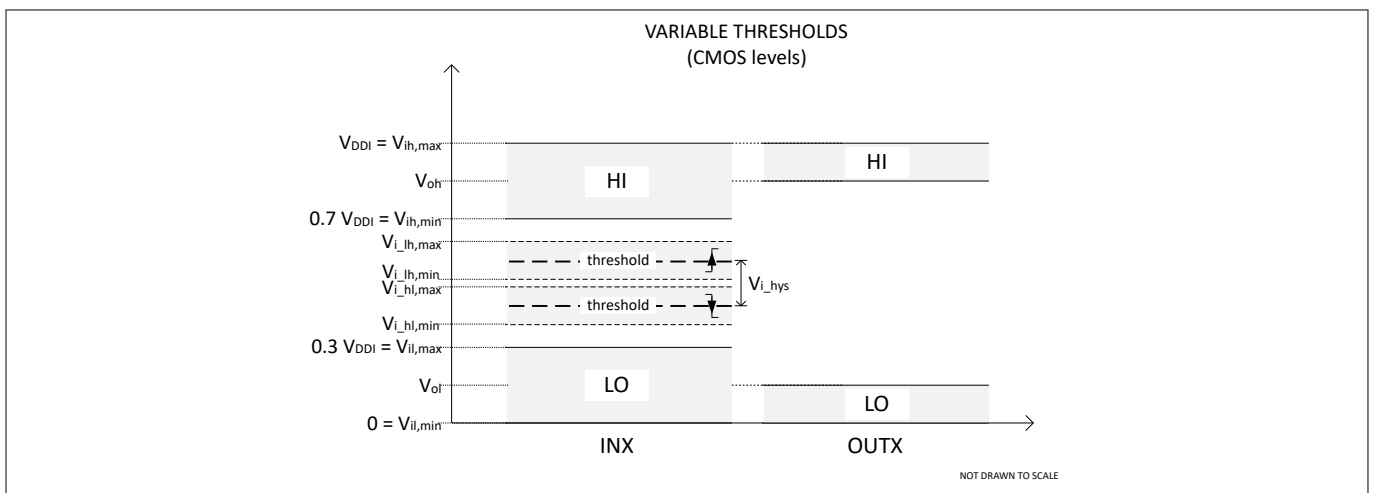


Figure 11 CMOS variable thresholds description

3 Functional description

3.5 Supply characteristics

Maximum values are given at $T_A = 125^\circ\text{C}$, $C_{\text{LOAD}} = 15 \text{ pF}$ and 50% duty cycle input square wave.

2+0 digital isolator (2DIB040xF)

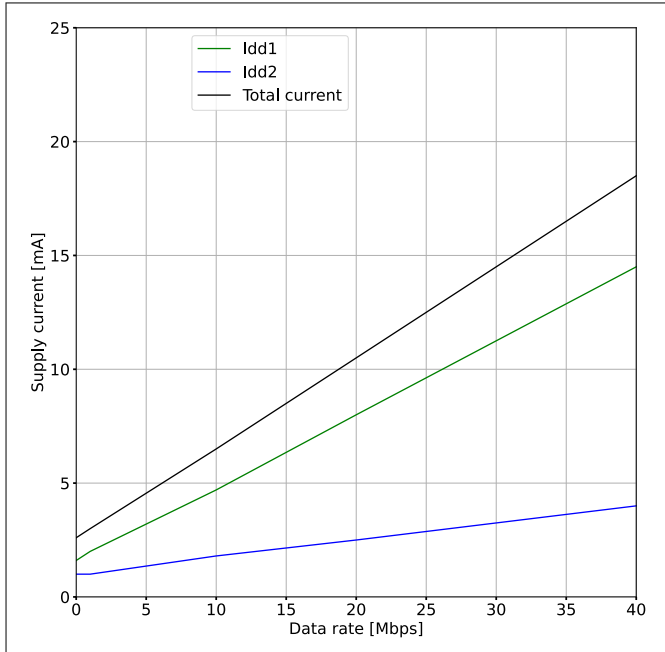


Figure 12 Supply current vs. data rate ($V_{\text{DD1}} = V_{\text{DD2}} = 2.7 \text{ V}$)

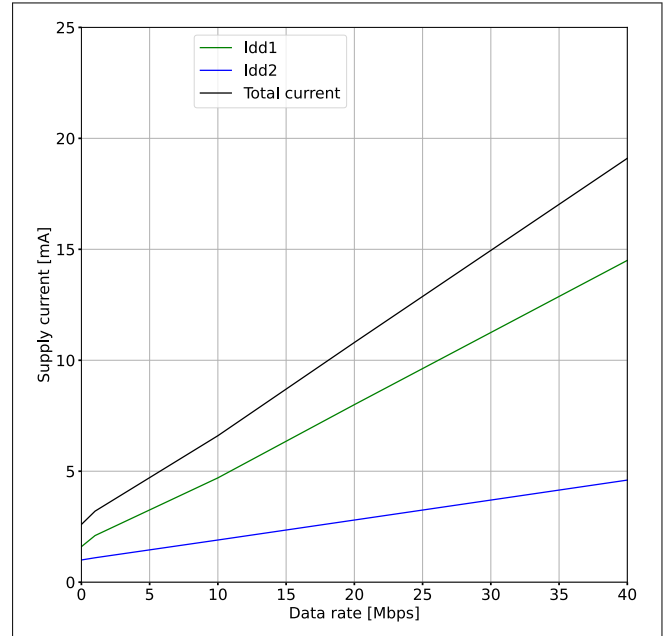


Figure 13 Supply current vs. data rate ($V_{\text{DD1}} = V_{\text{DD2}} = 3.3 \text{ V}$)

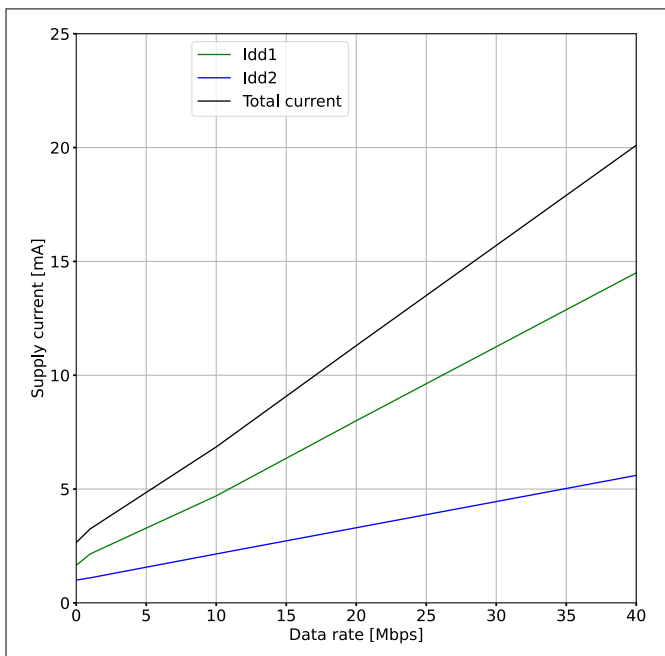


Figure 14 Supply current vs. data rate ($V_{\text{DD1}} = V_{\text{DD2}} = 5.0 \text{ V}$)

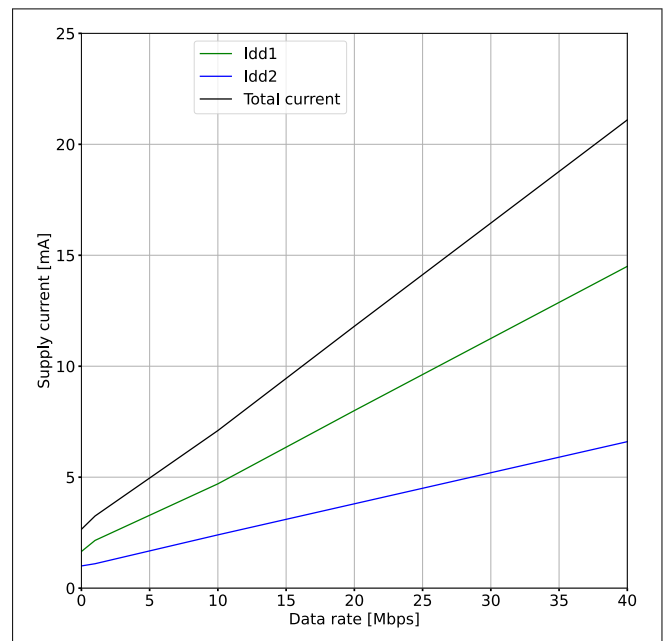


Figure 15 Supply current vs. data rate ($V_{\text{DD1}} = V_{\text{DD2}} = 6.5 \text{ V}$)

3 Functional description

1+1 digital isolator (2DIB140xF)

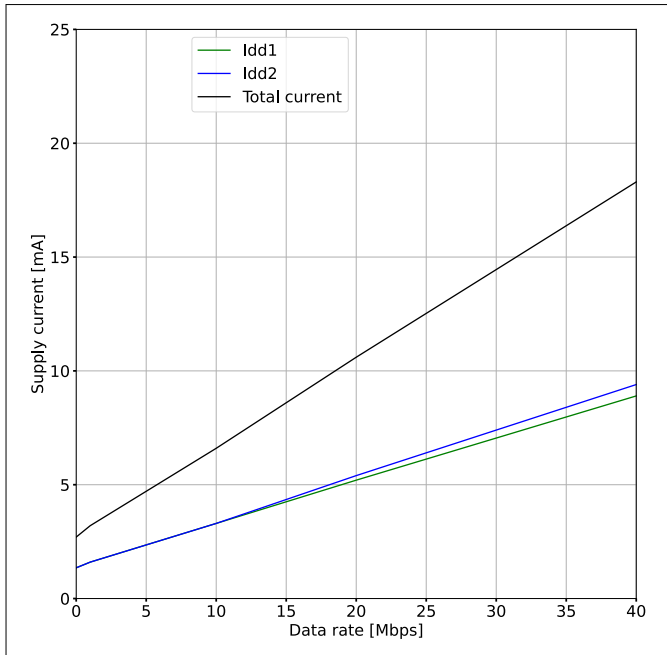


Figure 16 Supply current vs. data rate
 ($V_{DD1} = V_{DD2} = 2.7\text{ V}$)

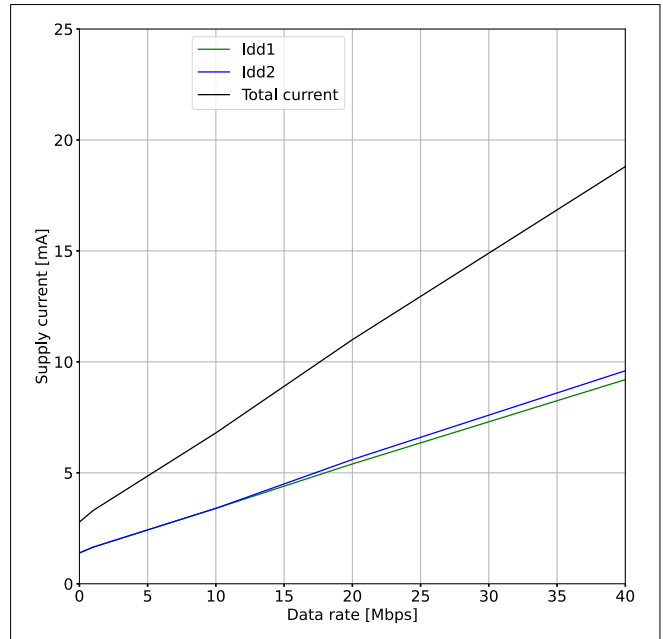


Figure 17 Supply current vs. data rate
 ($V_{DD1} = V_{DD2} = 3.3\text{ V}$)

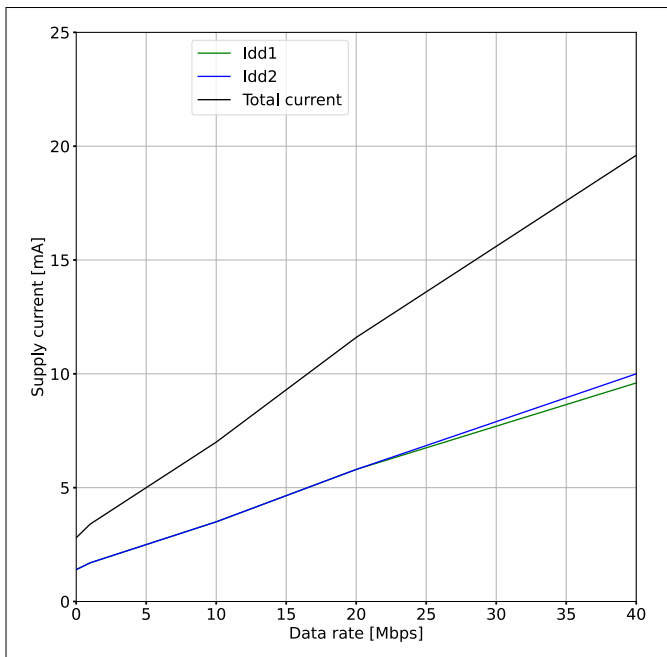


Figure 18 Supply current vs. data rate
 ($V_{DD1} = V_{DD2} = 5.0\text{ V}$)

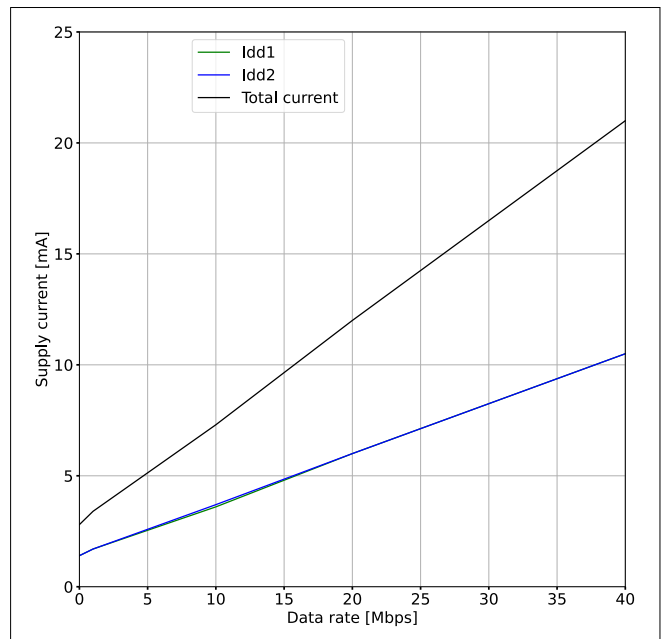


Figure 19 Supply current vs. data rate
 ($V_{DD1} = V_{DD2} = 6.5\text{ V}$)

4 Thermal and electrical characteristics

4 Thermal and electrical characteristics

4.1 Absolute maximum ratings

Table 4 Absolute maximum ratings

Stresses above the values listed below may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. These values are not tested during production test.

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
Supply voltage	V_{DD1}, V_{DD2}	-0.5		7.5	V	
Voltage at pins INx	V_{INX}	-0.5		$V_{DD1} + 0.5$	V	1) 2)
Voltage at pins OUTx	V_{OUTX}	- 0.5		$V_{DDO} + 0.5$	V	1)
Average output current per pin	I_{OUT}	-10		+10	mA	
Junction temperature	T_J	-40		150	°C	
Storage temperature	T_{STG}	-65		150	°C	
Soldering temperature	T_{SOL}			260	°C	reflow / wave soldering, according to JESD22A111
Electrostatic discharge HBM	V_{ESD_HBM}			2	kV	Human body model (HBM) according to JESD22-A114-B (discharging 100 pF capacitor through 1.5 kΩ resistor)
Electrostatic discharge CDM	V_{ESD_CDM}			500	V	Charged-device model (CDM) according to JESD22-002
Latch-up immunity	I_{LU}			150	mA	Latch-up immunity characterization according to JEDEC78E Class II, pin voltages according to abs. max. ratings

1) V_{DD1} and V_{DDO} refer to the supply voltages on the input and output sides of a given channel, respectively

2) Strongly driven inputs can power the V_{DD1} via an internal protection diode and can cause undetermined output

4.2 Additional ESD ratings

Table 5 Additional ESD ratings

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
Contact discharge per IEC 61000-4-2	$ V_{ESD_IEC} $		22		kV	Isolation barrier withstand test 1) 2)

1) IEC ESD strike is applied across the barrier with all pins on each side tied together, creating a two-terminal device

2) Testing is carried out in air or oil to determine the intrinsic contact discharge capability of the device

4 Thermal and electrical characteristics

4.3 Thermal characteristics

Typical thermal characteristics at $T_A = 25^\circ\text{C}$

Table 6 Thermal characteristics for JEDEC and reference PCB

Parameter	Symbol	JEDEC	Reference PCB	Unit	Note or condition
Thermal resistance junction-to-ambient	R_{thJA}	113 ¹⁾	89 ²⁾	K/W	JEDEC 2s2p (JED51-7), $P_{dis} = 186$ mW
Thermal resistance junction-to-case (top)	R_{thJC}	58	58	K/W	³⁾
Thermal resistance junction-to-board	R_{thJB}	35	44	K/W	⁴⁾
Characterization parameter junction-to-top	Ψ_{thJT}	7.5	7	K/W	⁵⁾
Characterization parameter junction-to-board	Ψ_{thJB}	34	43	K/W	⁵⁾

1) Obtained by simulating a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2a

2) Obtained by simulating a JEDEC-standard, high-K board, as specified in JESD51-7 and in reference PCB specifications below, in an environment described in JESD51-2a

3) Obtained by simulating a cold plate test on the package top. No specific JEDEC standard test exists, but a similar description can be found in the ANSI SEMI standard G30-88

4) Obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8

5) Estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining R_{th} , using a procedure described in JESD51-2a (sections 6 and 7)

Table 7 Reference PCB specifications

Parameter	Value	λ_{therm} [W/(m-K)]
Dimension [mm ³]	76.2 x 114.3 x 1.5 (JEDEC)	
Material	FR4	0.3
Metalization	JEDEC 2s2p (JESD 51-7)	388
Cooling area	Ground inner layer	
Thermal vias	$\varnothing = 0.5$ mm, plating 25 μm , 2 x 2 pcs. connected to inner ground layer	
Package attach [50 μm]	Solder	55
Inner ground layer [mm ³]	74.2 x 74.2 x 0.03 (JEDEC), planes are 4 mm spaced	

4 Thermal and electrical characteristics

Table 8 Reference PCB layout

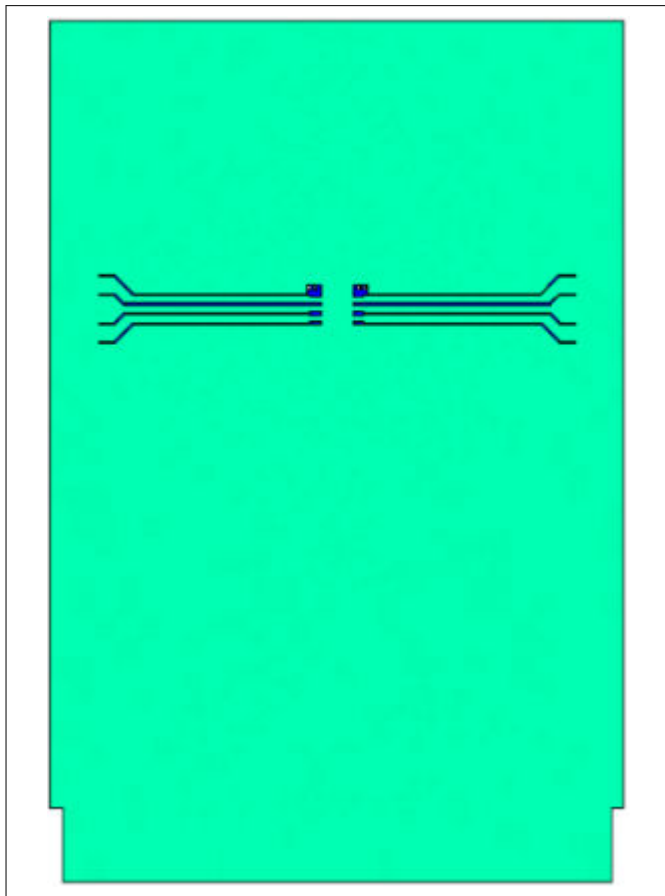


Figure 20 Top footprint

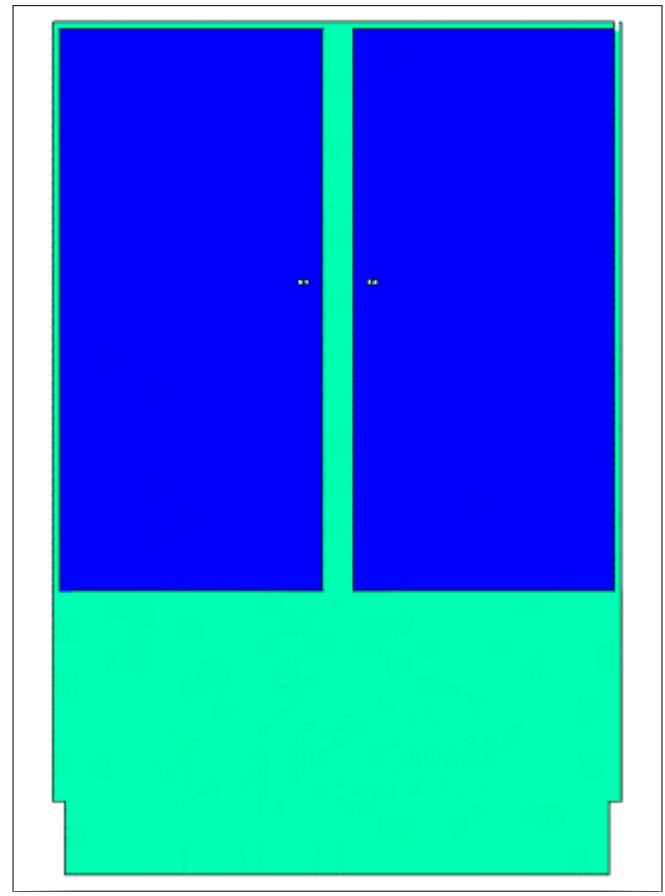


Figure 21 Inner layers (connect to ground)

4 Thermal and electrical characteristics

4.4 Operating range

Table 9 Operating range

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
Data rate	DR	0		40	Mbps	
Supply voltage	V_{DD1}, V_{DD2}	2.7		6.5	V	
High-level input voltage	V_{IH}	$0.7 V_{DI}$		V_{DDI}	V	
Low-level input voltage	V_{IL}	0		$0.3 V_{DI}$	V	
Ambient temperature	T_A	-40		125	°C	

4.5 Common-mode transient immunity (CMTI)

Table 10 Common-mode transient immunity (CMTI)

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
Static common-mode transient immunity (CMTI)	$ CM_H $	100			kV/μs	$V_{CM} = 1500\text{ V}; V_{INX}$ tied to V_{DDI} ^{1) 2) 3)}
Static common-mode transient immunity (CMTI)	$ CM_L $	100			kV/μs	$V_{CM} = 1500\text{ V}; V_{INX}$ tied to 0 V ^{2) 3)}

- 1) V_{DDI} refers to the supply voltages on the input side of a given channel
- 2) Minimum slew rate of a common-mode voltage at which the output signal is disturbed
- 3) Parameter not tested in production

4.6 Power supply - UVLO

Table 11 Power supply - UVLO

Typical values are given at $T_A = 25^\circ\text{C}$ over operating range unless otherwise specified. Minimum/maximum values apply over the recommended operating range of $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
Supply UVLO turn-on threshold	$V_{DDX(UVLOon)}$	2.42	2.55	2.68	V	
Supply UVLO turn-off threshold	$V_{DDX(UVLOoff)}$	2.35	2.45	2.55	V	
Supply UVLO hysteresis	$V_{DDX(UVLOhys)}$	0.07	0.10		V	

4 Thermal and electrical characteristics

4.7 Electrical characteristics

The electrical characteristics describe the behavior of the device under the specified operating conditions.

4.7.1 Electrical characteristics - 6.5 V supply

Typical values are given at $T_A = 25^\circ\text{C}$ with $V_{DD1} = V_{DD2} = 6.5\text{ V}$. Minimum/maximum specifications apply over the entire recommended operation range of $V_{DD1} = V_{DD2} = 6.5\text{ V}$, and $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$, unless otherwise noted. Switching characteristics are tested with $C_{LOAD} = 15\text{ pF}$ and 50% duty-cycle input square wave, over operating range unless otherwise specified. Supply current values are specified considering that all channels are switching at the same data rate. Parameters are not tested in production unless otherwise specified.

4.7.1.1 Logic inputs

Table 12 Logic inputs

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
High-level input current	I_{IH}			10	μA	$V_{INX} = V_{DDI}$ ^{1) 2)}
Low-level input current	I_{IL}	-10			μA	$V_{INX} = 0\text{ V}$ ²⁾
Input voltage threshold for transition LH	V_{I_LH}			$0.7 V_{D_DI}$	V	
Input voltage threshold for transition HL	V_{I_HL}	$0.3 V_{D_DI}$			V	
Input voltage threshold hysteresis	V_{I_HYS}	$0.1 V_{D_DI}$			V	
Input pull-down resistor	R_{IN}		825		$\text{k}\Omega$	$V_{INX} = V_{DDI}$ ^{1) 2)}

1) V_{DDI} = Input-side supply voltage. For input channels on side 1 it is V_{DD1} and for input channels on side 2 it is V_{DD2}
 2) Parameter tested in production

4.7.1.2 Logic outputs

Table 13 Logic outputs

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
High-level output voltage	V_{OH}	$V_{DDO} - 0.4$			V	$I_{OH} = 4\text{ mA}$ ¹⁾
Low-level output voltage	V_{OL}			0.4	V	$I_{OL} = -4\text{ mA}$

1) V_{DDO} - Output-side supply voltage. For output buffers on side 1 it is V_{DD1} and for output buffers on side 2 it is V_{DD2}

4 Thermal and electrical characteristics

4.7.1.3 Power supply - 2DIB040xF (2+0)

Table 14 Power supply - 2DIB040xF (2+0)

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
Supply current - DC input	I_{DD1}			1.65	mA	$V_{INx} = V_{DD1}$
Supply current - DC input	I_{DD2}			1	mA	$V_{INx} = V_{DD1}$
Supply current - DC input	I_{DD1}			1.65	mA	$V_{INx} = 0\text{ V}$
Supply current - DC input	I_{DD2}			1	mA	$V_{INx} = 0\text{ V}$
Supply current - AC input	I_{DD1_1Mb}			2.15	mA	$DR = 1\text{ Mbps}$
Supply current - AC input	I_{DD2_1Mb}			1.2	mA	$DR = 1\text{ Mbps}$
Supply current - AC input	I_{DD1_10Mb}			4.7	mA	$DR = 10\text{ Mbps}$
Supply current - AC input	I_{DD2_10Mb}			2.4	mA	$DR = 10\text{ Mbps}$
Supply current - AC input	I_{DD1_20Mb}			8	mA	$DR = 20\text{ Mbps}$
Supply current - AC input	I_{DD2_20Mb}			3.8	mA	$DR = 20\text{ Mbps}$
Supply current - AC input	I_{DD1_40Mb}			14.5	mA	$DR = 40\text{ Mbps}$
Supply current - AC input	I_{DD2_40Mb}			6.6	mA	$DR = 40\text{ Mbps}$

4 Thermal and electrical characteristics

4.7.1.4 Power supply - 2DIB140xF (1+1)

Table 15 Power supply - 2DIB140xF (1+1)

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
Supply current - DC input	I_{DD1}			1.4	mA	$V_{INx} = V_{DDI}$ ¹⁾
Supply current - DC input	I_{DD2}			1.4	mA	$V_{INx} = V_{DDI}$ ¹⁾
Supply current - DC input	I_{DD1}			1.4	mA	$V_{INx} = 0\text{ V}$
Supply current - DC input	I_{DD2}			1.4	mA	$V_{INx} = 0\text{ V}$
Supply current - AC input	I_{DD1_1Mb}			1.7	mA	$DR = 1\text{ Mbps}$
Supply current - AC input	I_{DD2_1Mb}			1.7	mA	$DR = 1\text{ Mbps}$
Supply current - AC input	I_{DD1_10Mb}			3.6	mA	$DR = 10\text{ Mbps}$
Supply current - AC input	I_{DD2_10Mb}			3.7	mA	$DR = 10\text{ Mbps}$
Supply current - AC input	I_{DD1_20Mb}			6	mA	$DR = 20\text{ Mbps}$
Supply current - AC input	I_{DD2_20Mb}			6	mA	$DR = 20\text{ Mbps}$
Supply current - AC input	I_{DD1_40Mb}			10.5	mA	$DR = 40\text{ Mbps}$
Supply current - AC input	I_{DD2_40Mb}			10.5	mA	$DR = 40\text{ Mbps}$

1) V_{DDI} - Input-side supply voltage. For input channels on side 1 it is V_{DD1} and for input channels on side 2 it is V_{DD2}

4 Thermal and electrical characteristics

4.7.1.5 Dynamic characteristics

Table 16 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
INx to OUTx turn-on propagation delay	t_{PDOn}	21	27	33	ns	From 50% level of rising input to 50% level of corresponding rising output ¹⁾
INx to OUTx turn-off propagation delay	t_{PDoff}	21	27	33	ns	From 50% level of falling input to 50% level of corresponding falling output ¹⁾
Part-to-part propagation delays mismatch	$\Delta t_{PD,p-p}$			6	ns	^{1) 2)}
Codirectional channel-to-channel propagation delay mismatch	$\Delta t_{PD,Ch-Ch}$			3	ns	Within same sample, over operating temperature range, same-direction channels, switching in the same direction ¹⁾
Opposite-directional channel-to-channel propagation delay mismatch	$\Delta t_{PD,Ch-Ch}$			3	ns	Within same sample, over operating temperature range, opposite-directional channels, switching with the same signal level ¹⁾
Pulse width distortion	PWD			4	ns	$ t_{PDoff} - t_{PDOn} $ ^{1) 3)}
Input pulse width that changes output state	$t_{pw,min}$	9	12	16	ns	Measured with full range of input signal $V_{IN} = V_{DDI}$ ⁴⁾
Output signal rise time	t_{rise}			4	ns	10% to 90% rising output, $C_{LOAD} = 15$ pF
Output signal fall time	t_{fall}			4	ns	90% to 10% falling output, $C_{LOAD} = 15$ pF
Default output delay time from input power loss	t_{DO}		0.4	2.6	μs	Measured from $V_{DDX(UVLOoff)} = 2.55$ V. Power supply ramp rate = 1 V/ μs
Time from UVLO to valid output data	t_{PU}			3	μs	Power supply ramp rate = 1 V/ μs , DR > 6.6 Mbps

- 1) Parameter tested in production
- 2) The parameter gives the difference in propagation delay between different samples switching in the same direction under same conditions, including same ambient temperature
- 3) Also known as pulse skew. The parameter gives the maximum difference between on and off propagation delay shown from the same sample over the operating temperature range
- 4) V_{DDI} = Input-side supply voltage. For input channels on side 1 it is V_{DD1} and for input channels on side 2 it is V_{DD2}

4 Thermal and electrical characteristics

4.7.2 Electrical characteristics - 5 V supply

Typical values are given at $T_A = 25^\circ\text{C}$, $V_{DD1} = V_{DD2} = 5\text{ V}$. Minimum/maximum specifications apply over the entire recommended operation range of $V_{DD1} = V_{DD2} = 5\text{ V} \pm 10\%$, and $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$, unless otherwise noted. Switching characteristics are tested with $C_{LOAD} = 15\text{ pF}$ and 50% duty-cycle input square wave, over operating range unless otherwise specified. Supply current values are specified considering that all channels are switching at the same data rate. Parameters are tested in production unless otherwise specified. Supply current values are tested in production for data rates up to 1 Mbps.

4.7.2.1 Logic inputs

Table 17 Logic inputs

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
High-level input current	I_{IH}			10	μA	$V_{INX} = V_{DDI}$ ¹⁾
Low-level input current	I_{IL}	-10			μA	$V_{INX} = 0\text{ V}$
Input voltage threshold for transition LH	V_{I_LH}			$0.7 V_{D_DI}$	V	
Input voltage threshold for transition HL	V_{I_HL}	$0.3 V_{D_DI}$			V	
Input voltage threshold hysteresis	V_{I_HYS}	$0.1 V_{D_DI}$			V	
Input pull-down resistor	R_{IN}		825		$\text{k}\Omega$	$V_{INX} = V_{DDI}$ ¹⁾

1) V_{DDI} - Input-side supply voltage. For input channels on side 1 it is V_{DD1} and for input channels on side 2 it is V_{DD2}

4.7.2.2 Logic outputs

Table 18 Logic outputs

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
High-level output voltage	V_{OH}	$V_{DDO} - 0.4$			V	$I_{OH} = 4\text{ mA}$ ¹⁾
Low-level output voltage	V_{OL}			0.4	V	$I_{OL} = -4\text{ mA}$

1) V_{DDO} - Output-side supply voltage. For output buffers on side 1 it is V_{DD1} and for output buffers on side 2 it is V_{DD2}

4 Thermal and electrical characteristics

4.7.2.3 Power supply - 2DIB040xF (2+0)

Table 19 Power supply - 2DIB040xF (2+0)

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
Supply current - DC input	I_{DD1}			1.65	mA	$V_{INx} = V_{DD1}$
Supply current - DC input	I_{DD2}			1	mA	$V_{INx} = V_{DD1}$
Supply current - DC input	I_{DD1}			1.65	mA	$V_{INx} = 0\text{ V}$
Supply current - DC input	I_{DD2}			1	mA	$V_{INx} = 0\text{ V}$
Supply current - AC input	I_{DD1_1Mb}			2.15	mA	$DR = 1\text{ Mbps}$
Supply current - AC input	I_{DD2_1Mb}			1.1	mA	$DR = 1\text{ Mbps}$
Supply current - AC input	I_{DD1_10Mb}			4.7	mA	$DR = 10\text{ Mbps}$
Supply current - AC input	I_{DD2_10Mb}			2.15	mA	$DR = 10\text{ Mbps}$
Supply current - AC input	I_{DD1_20Mb}			8	mA	$DR = 20\text{ Mbps}$
Supply current - AC input	I_{DD2_20Mb}			3.3	mA	$DR = 20\text{ Mbps}$
Supply current - AC input	I_{DD1_40Mb}			14.5	mA	$DR = 40\text{ Mbps}$
Supply current - AC input	I_{DD2_40Mb}			5.6	mA	$DR = 40\text{ Mbps}$

4 Thermal and electrical characteristics

4.7.2.4 Power supply - 2DIB140xF (1+1)

Table 20 Power supply - 2DIB140xF (1+1)

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
Supply current - DC input	I_{DD1}			1.4	mA	$V_{INx} = V_{DDI}$ ¹⁾
Supply current - DC input	I_{DD2}			1.4	mA	$V_{INx} = V_{DDI}$ ¹⁾
Supply current - DC input	I_{DD1}			1.4	mA	$V_{INx} = 0\text{ V}$
Supply current - DC input	I_{DD2}			1.4	mA	$V_{INx} = 0\text{ V}$
Supply current - AC input	I_{DD1_1Mb}			1.7	mA	$DR = 1\text{ Mbps}$
Supply current - AC input	I_{DD2_1Mb}			1.7	mA	$DR = 1\text{ Mbps}$
Supply current - AC input	I_{DD1_10Mb}			3.5	mA	$DR = 10\text{ Mbps}$
Supply current - AC input	I_{DD2_10Mb}			3.5	mA	$DR = 10\text{ Mbps}$
Supply current - AC input	I_{DD1_20Mb}			5.8	mA	$DR = 20\text{ Mbps}$
Supply current - AC input	I_{DD2_20Mb}			5.8	mA	$DR = 20\text{ Mbps}$
Supply current - AC input	I_{DD1_40Mb}			9.6	mA	$DR = 40\text{ Mbps}$
Supply current - AC input	I_{DD2_40Mb}			10	mA	$DR = 40\text{ Mbps}$

1) V_{DDI} - Input-side supply voltage. For input channels on side 1 it is V_{DD1} and for input channels on side 2 it is V_{DD2}

4 Thermal and electrical characteristics

4.7.2.5 Dynamic characteristics

Table 21 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
INx to OUTx turn-on propagation delay	t_{PDOn}	21	26.4	32	ns	From 50% level of rising input to 50% level of corresponding rising output
INx to OUTx turn-off propagation delay	t_{PDoff}	21	26.4	32	ns	From 50% level of falling input to 50% level of corresponding falling output
Part-to-part propagation delays mismatch	$\Delta t_{PD,p-p}$			6	ns	¹⁾
Codirectional channel-to-channel propagation delay mismatch	$\Delta t_{PD,Ch-Ch}$			3	ns	Within same sample, over operating temperature range, same-direction channels, switching in the same direction
Opposite-directional channel-to-channel propagation delay mismatch	$\Delta t_{PD,Ch-Ch}$			3	ns	Within same sample, over operating temperature range, opposite-directional channels, switching with the same signal level.
Pulse width distortion	PWD			3	ns	$ t_{PDoff} - t_{PDOn} $ ²⁾
Input pulse width that changes output state	$t_{pw,min}$	9	11.5	15	ns	Measured with full range of input signal $V_{IN} = V_{DDI}$ ³⁾
Output signal rise time	t_{rise}			3.5	ns	10% to 90% rising output, $C_{LOAD} = 15 \text{ pF}$ ⁴⁾
Output signal fall time	t_{fall}			3.5	ns	90% to 10% falling output, $C_{LOAD} = 15 \text{ pF}$ ⁴⁾
Default output delay time from input power loss	t_{DO}		0.4	2.6	μs	Measured from $V_{DDX(UVLOoff)} = 2.55 \text{ V}$. Power supply ramp rate = $1 \text{ V}/\mu\text{s}$ ⁵⁾
Time from UVLO to valid output data	t_{PU}			3	μs	Power supply ramp rate = $1 \text{ V}/\mu\text{s}$, $DR > 6.6 \text{ Mbps}$ ⁴⁾

- 1) The parameter gives the difference in propagation delay between different samples switching in the same direction under same conditions, including same ambient temperature
- 2) Also known as pulse skew. The parameter gives the maximum difference between on and off propagation delay shown from the same sample over the operating temperature range
- 3) V_{DDI} - Input-side supply voltage. For input channels on side 1 it is V_{DD1} and for input channels on side 2 it is V_{DD2}
- 4) Parameter not tested in production
- 5) Maximum value tested in production

4 Thermal and electrical characteristics

4.7.3 Electrical characteristics - 3.3 V supply

Typical values are given at $T_A = 25^\circ\text{C}$, $V_{DD1} = V_{DD2} = 3.3\text{ V}$. Minimum/maximum specifications apply over the entire recommended operation range of $V_{DD1} = V_{DD2} = 3.3\text{ V} \pm 10\%$, and $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$, unless otherwise noted. Switching characteristics are tested with $C_{LOAD} = 15\text{ pF}$ and 50% duty-cycle input square wave, over operating range unless otherwise specified. Supply current values are specified considering that all channels are switching at the same data rate. Parameters are tested in production unless otherwise specified. Supply current values are tested in production only for data rates up to 1 Mbps.

4.7.3.1 Logic inputs

Table 22 Logic inputs

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
High-level input current	I_{IH}			10	μA	$V_{INX} = V_{DDI}$ ¹⁾
Low-level input current	I_{IL}	-10			μA	$V_{INX} = 0\text{ V}$
Input voltage threshold for transition LH	V_{I_LH}			$0.7 V_{D_DI}$	V	
Input voltage threshold for transition HL	V_{I_HL}	$0.3 V_{D_DI}$			V	
Input voltage threshold hysteresis	V_{I_HYS}	$0.1 V_{D_DI}$			V	
Input pull-down resistor	R_{IN}		825		$\text{k}\Omega$	$V_{INX} = V_{DDI}$ ¹⁾

1) V_{DDI} - Input-side supply voltage. For input channels on side 1 it is V_{DD1} and for input channels on side 2 it is V_{DD2}

4.7.3.2 Logic outputs

Table 23 Logic outputs

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
High-level output voltage	V_{OH}	$V_{DDO} - 0.3$			V	$I_{OH} = 2\text{ mA}$ ¹⁾
Low-level output voltage	V_{OL}			0.3	V	$I_{OL} = -2\text{ mA}$

1) V_{DDO} - Output-side supply voltage. For output buffers on side 1 it is V_{DD1} and for output buffers on side 2 it is V_{DD2}

4 Thermal and electrical characteristics

4.7.3.3 Power supply - 2DIB040xF (2+0)

Table 24 Power supply - 2DIB040xF (2+0)

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
Supply current - DC input	I_{DD1}			1.6	mA	$V_{INx} = V_{DD1}$
Supply current - DC input	I_{DD2}			1	mA	$V_{INx} = V_{DD1}$
Supply current - DC input	I_{DD1}			1.6	mA	$V_{INx} = 0\text{ V}$
Supply current - DC input	I_{DD2}			1	mA	$V_{INx} = 0\text{ V}$
Supply current - AC input	I_{DD1_1Mb}			2.1	mA	$DR = 1\text{ Mbps}$
Supply current - AC input	I_{DD2_1Mb}			1.1	mA	$DR = 1\text{ Mbps}$
Supply current - AC input	I_{DD1_10Mb}			4.7	mA	$DR = 10\text{ Mbps}$
Supply current - AC input	I_{DD2_10Mb}			1.9	mA	$DR = 10\text{ Mbps}$
Supply current - AC input	I_{DD1_20Mb}			8	mA	$DR = 20\text{ Mbps}$
Supply current - AC input	I_{DD2_20Mb}			2.8	mA	$DR = 20\text{ Mbps}$
Supply current - AC input	I_{DD1_40Mb}			14.5	mA	$DR = 40\text{ Mbps}$
Supply current - AC input	I_{DD2_40Mb}			4.6	mA	$DR = 40\text{ Mbps}$

4 Thermal and electrical characteristics

4.7.3.4 Power supply - 2DIB140xF (1+1)

Table 25 Power supply - 2DIB140xF (1+1)

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
Supply current - DC input	I_{DD1}			1.39	mA	$V_{INx} = V_{DDI}$ ¹⁾
Supply current - DC input	I_{DD2}			1.39	mA	$V_{INx} = V_{DDI}$ ¹⁾
Supply current - DC input	I_{DD1}			1.39	mA	$V_{INx} = 0\text{ V}$
Supply current - DC input	I_{DD2}			1.39	mA	$V_{INx} = 0\text{ V}$
Supply current - AC input	I_{DD1_1Mb}			1.65	mA	$DR = 1\text{ Mbps}$
Supply current - AC input	I_{DD2_1Mb}			1.65	mA	$DR = 1\text{ Mbps}$
Supply current - AC input	I_{DD1_10Mb}			3.4	mA	$DR = 10\text{ Mbps}$
Supply current - AC input	I_{DD2_10Mb}			3.5	mA	$DR = 10\text{ Mbps}$
Supply current - AC input	I_{DD1_20Mb}			5.4	mA	$DR = 20\text{ Mbps}$
Supply current - AC input	I_{DD2_20Mb}			5.6	mA	$DR = 20\text{ Mbps}$
Supply current - AC input	I_{DD1_40Mb}			9.2	mA	$DR = 40\text{ Mbps}$
Supply current - AC input	I_{DD2_40Mb}			9.6	mA	$DR = 40\text{ Mbps}$

1) V_{DDI} - Input-side supply voltage. For input channels on side 1 it is V_{DD1} and for input channels on side 2 it is V_{DD2}

4 Thermal and electrical characteristics

4.7.3.5 Dynamic characteristics

Table 26 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
INx to OUTx turn-on propagation delay	t_{PDOn}	21	26	32	ns	From 50% level of rising input to 50% level of corresponding rising output
INx to OUTx turn-off propagation delay	t_{PDoff}	21	26	32	ns	From 50% level of falling input to 50% level of corresponding falling output
Part-to-part propagation delays mismatch	$\Delta t_{PD,p-p}$			6	ns	¹⁾
Codirectional channel-to-channel propagation delay mismatch	$\Delta t_{PD,Ch-Ch}$			3	ns	Within same sample, over operating temperature range, same-direction channels, switching in the same direction
Opposite-directional channel-to-channel propagation delay mismatch	$\Delta t_{PD,Ch-Ch}$			3	ns	Within same sample, over operating temperature range, opposite-directional channels, switching with the same signal level
Pulse width distortion	PWD			3	ns	$ t_{PDoff} - t_{PDOn} $ ²⁾
Input pulse width that changes output state	$t_{pw,min}$	10	11.5	15	ns	Measured with full range of input signal $V_{IN} = V_{DDI}$ ³⁾
Output signal rise time	t_{rise}			3.5	ns	10% to 90% rising output, $C_{LOAD} = 15 \text{ pF}$ ⁴⁾
Output signal fall time	t_{fall}			3.5	ns	90% to 10% falling output, $C_{LOAD} = 15 \text{ pF}$ ⁴⁾
Default output delay time from input power loss	t_{DO}		0.4	2.6	μs	Measured from $V_{DDX(UVLOoff)} = 2.55 \text{ V}$. Power supply ramp rate = $1 \text{ V}/\mu\text{s}$ ⁵⁾
Time from UVLO to valid output data	t_{PU}			3	μs	Power supply ramp rate = $1 \text{ V}/\mu\text{s}$, $DR > 6.6 \text{ Mbps}$ ⁴⁾

- 1) The parameter gives the difference in propagation delay between different samples switching in the same direction under same conditions, including same ambient temperature
- 2) Also known as pulse skew. The parameter gives the maximum difference between on and off propagation delay shown from the same sample over the operating temperature range
- 3) V_{DDI} - Input-side supply voltage. For input channels on side 1 it is V_{DD1} and for input channels on side 2 it is V_{DD2}
- 4) Parameter not tested in production
- 5) Maximum value tested in production

4 Thermal and electrical characteristics

4.7.4 Electrical characteristics - 2.7 V supply

Typical values are given at $T_A = 25^\circ\text{C}$ with $V_{DD1} = V_{DD2} = 2.7\text{ V}$. Minimum/maximum specifications apply over the entire recommended operation range of $V_{DD1} = V_{DD2} = 2.7\text{ V}$, and $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$, unless otherwise noted. Switching characteristics are tested with $C_{LOAD} = 15\text{ pF}$ and 50% duty-cycle input square wave, over operating range unless otherwise specified. Supply current values are specified considering that all channels are switching at the same data rate. Parameters are not tested in production unless otherwise specified.

4.7.4.1 Logic inputs

Table 27 Logic inputs

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
High-level input current	I_{IH}			10	μA	$V_{INX} = V_{DDI}$ ^{1) 2)}
Low-level input current	I_{IL}	-10			μA	$V_{INX} = 0\text{ V}$ ²⁾
Input voltage threshold for transition LH	V_{I_LH}			$0.7 V_{DI}$	V	
Input voltage threshold for transition HL	V_{I_HL}	$0.3 V_{DI}$			V	
Input voltage threshold hysteresis	V_{I_HYS}	$0.1 V_{DI}$			V	
Input pull-down resistor	R_{IN}		825		$\text{k}\Omega$	$V_{INX} = V_{DDI}$ ^{1) 2)}

1) V_{DDI} - Input-side supply voltage. For input channels on side 1 it is V_{DD1} and for input channels on side 2 it is V_{DD2}
 2) Parameter tested in production

4.7.4.2 Logic outputs

Table 28 Logic outputs

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
High-level output voltage	V_{OH}	$V_{DDO} - 0.3$			V	$I_{OH} = 1\text{ mA}$ ¹⁾
Low-level output voltage	V_{OL}			0.3	V	$I_{OL} = -1\text{ mA}$

1) V_{DDO} - Output-side supply voltage. For output buffers on side 1 it is V_{DD1} and for output buffers on side 2 it is V_{DD2}

4 Thermal and electrical characteristics

4.7.4.3 Power supply - 2DIB040xF (2+0)

Table 29 Power supply - 2DIB040xF (2+0)

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
Supply current - DC input	I_{DD1}			1.6	mA	$V_{INx} = V_{DD1}$
Supply current - DC input	I_{DD2}			1	mA	$V_{INx} = V_{DD1}$
Supply current - DC input	I_{DD1}			1.6	mA	$V_{INx} = 0\text{ V}$
Supply current - DC input	I_{DD2}			1	mA	$V_{INx} = 0\text{ V}$
Supply current - AC input	I_{DD1_1Mb}			2	mA	$DR = 1\text{ Mbps}$
Supply current - AC input	I_{DD2_1Mb}			1	mA	$DR = 1\text{ Mbps}$
Supply current - AC input	I_{DD1_10Mb}			4.7	mA	$DR = 10\text{ Mbps}$
Supply current - AC input	I_{DD2_10Mb}			1.8	mA	$DR = 10\text{ Mbps}$
Supply current - AC input	I_{DD1_20Mb}			8	mA	$DR = 20\text{ Mbps}$
Supply current - AC input	I_{DD2_20Mb}			2.5	mA	$DR = 20\text{ Mbps}$
Supply current - AC input	I_{DD1_40Mb}			14.5	mA	$DR = 40\text{ Mbps}$
Supply current - AC input	I_{DD2_40Mb}			4	mA	$DR = 40\text{ Mbps}$

4 Thermal and electrical characteristics

4.7.4.4 Power supply - 2DIB140xF (1+1)

Table 30 Power supply - 2DIB140xF (1+1)

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
Supply current - DC input	I_{DD1}			1.35	mA	$V_{INx} = V_{DD1}$
Supply current - DC input	I_{DD2}			1.35	mA	$V_{INx} = V_{DD2}$
Supply current - DC input	I_{DD1}			1.35	mA	$V_{INx} = GND1$
Supply current - DC input	I_{DD2}			1.35	mA	$V_{INx} = GND2$
Supply current - AC input	I_{DD1_1Mb}			1.6	mA	$DR = 1$ Mbps
Supply current - AC input	I_{DD2_1Mb}			1.6	mA	$DR = 1$ Mbps
Supply current - AC input	I_{DD1_10Mb}			3.3	mA	$DR = 10$ Mbps
Supply current - AC input	I_{DD2_10Mb}			3.3	mA	$DR = 10$ Mbps
Supply current - AC input	I_{DD1_20Mb}			5.2	mA	$DR = 20$ Mbps
Supply current - AC input	I_{DD2_20Mb}			5.4	mA	$DR = 20$ Mbps
Supply current - AC input	I_{DD1_40Mb}			8.9	mA	$DR = 40$ Mbps
Supply current - AC input	I_{DD2_40Mb}			9.4	mA	$DR = 40$ Mbps

4 Thermal and electrical characteristics

4.7.4.5 Dynamic characteristics

Table 31 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
INx to OUTx turn-on propagation delay	t_{PDOn}	21	26	32	ns	From 50% level of rising input to 50% level of corresponding rising output ¹⁾
INx to OUTx turn-off propagation delay	t_{PDoff}	21	26	32	ns	From 50% level of falling input to 50% level of corresponding falling output ¹⁾
Part-to-part propagation delays mismatch	$\Delta t_{PD,p-p}$			6	ns	^{1) 2)}
Codirectional channel-to-channel propagation delay mismatch	$\Delta t_{PD,Ch-Ch}$			3	ns	Within same sample, over operating temperature range, same-direction channels, switching in the same direction ¹⁾
Opposite-directional channel-to-channel propagation delay mismatch	$\Delta t_{PD,Ch-Ch}$			3	ns	Within same sample, over operating temperature range, opposite-directional channels, switching with the same signal level ¹⁾
Pulse width distortion	PWD			3.5	ns	$ t_{PDoff} - t_{PDOn} $ ^{1) 3)}
Input pulse width that changes output state	$t_{pw,min}$	9	11.5	15	ns	Measured with the full range of input signal $V_{IN} = V_{DDI}$ ^{1) 4)}
Output signal rise time	t_{rise}			3	ns	10% to 90% rising output, $C_{LOAD} = 15$ pF
Output signal fall time	t_{fall}			3	ns	90% to 10% falling output, $C_{LOAD} = 15$ pF
Default output delay time from input power loss	t_{DO}		0.4	2.6	μs	Measured from $V_{DDX(UVLOoff)} = 2.55$ V. Power supply ramp rate = 1 V/ μs
Time from UVLO to valid output data	t_{PU}			3	μs	Power supply ramp rate = 1 V/ μs , DR > 6.6 Mbps

- 1) Parameter tested in production
- 2) The parameter gives the difference in propagation delay between different samples switching in the same direction under same conditions, including same ambient temperature
- 3) Also known as pulse skew. The parameter gives the maximum difference between on and off propagation delay shown from the same sample over the operating temperature range
- 4) V_{DDI} = Input-side supply voltage. For input channels on side 1 it is V_{DD1} and for input channels on side 2 it is V_{DD2}

4 Thermal and electrical characteristics

4.8 Insulation and safety-related specifications

This digital isolator is suitable for the rated insulation only within the safety-limiting values. Compliance with these safety-limiting values must be ensured by means of suitable protective circuits.

4.8.1 Insulation characteristics

Parameter	Symbol	Value	Unit	Note or condition
External clearance	<i>CLR</i>	>4	mm	Shortest distance in air from any input pin to any output pin according to IEC 60664-1 ¹⁾
External creepage	<i>CRP</i>	>4	mm	Shortest distance over package surface from any input pin to any output pin according to IEC 60664-1 ¹⁾
Comparative tracking index	<i>CTI</i>	>400	V	According to IEC 60112
Material group		II		According to IEC 60112
Pollution degree		2		According to IEC 60664-1
Overvoltage category according to IEC 60664-1	-	I - IV		Rated mains voltage $\leq 150 V_{rms}$
	-	I - III		Rated mains voltage $\leq 300 V_{rms}$
	-	I - II		Rated mains voltage $\leq 600 V_{rms}$
	-	I		Rated mains voltage $\leq 1000 V_{rms}$
Climatic category		40/125 /21		

Input-to-output isolation according to UL1577 Ed. 5 ²⁾

Input-to-output isolation voltage	V_{ISO}	3000	V_{rms}	$V_{TEST} = V_{ISO}$ for $t = 60$ s (qualification); $V_{TEST} = 1.2 \times V_{ISO}$ for $t = 1$ s (100% productive tests)
-----------------------------------	-----------	------	-----------	---

Input-to-output isolation according to DIN VDE 0884-17, IEC 60747-17 ³⁾

Maximum rated transient isolation voltage	V_{IOTM}	4242	V_{pk}	$V_{TEST} = 1.2 \times V_{IOTM}$ for $t_{ini} = 1$ s
Maximum impulse voltage	V_{IMP}	4242	V_{pk}	According to IEC 60664-1, IEC 60747-17
Maximum rated repetitive isolation voltage	V_{IORM}	1000	V_{pk}	
Apparent charge	q_{PD}	<5	pC	Method (b1) (routine test and type test preconditioning) $V_{PD(iini)} = 1.2 \times V_{IOTM}$ for $t_{ini} = 1$ s $V_{PD(m)} > 1.65 \times V_{IORM}$ for $t_m = 1$ s ⁴⁾ Method (a) (type test, subgroup 1 final measurements) $V_{PD(iini)} = V_{IOTM}$ for $t_{ini} = 60$ s $V_{PD(m)} = 1.3 \times V_{IORM}$ for $t_m = 10$ s

4 Thermal and electrical characteristics

Parameter	Symbol	Value	Unit	Note or condition
Maximum surge isolation voltage	V_{IOSM}	6000	V_{pk}	$V_{TEST} = 1.3 \times V_{IOSM}$ ⁵⁾
Isolation resistance ⁷⁾	R_{IO}	$>10^{12}$	Ω	$V_{IO} = 500 V_{dc}$ for $t = 60$ s, $T_A = 25^\circ C$ ⁶⁾
		$>10^{11}$	Ω	$V_{IO} = 500 V_{dc}$ for $t = 60$ s, $T_A = 25^\circ C$ ⁶⁾
	R_{IO_S}	$>10^9$	Ω	$V_{IO} = 500 V_{dc}$ for $t = 60$ s, $T_A = T_S = 150^\circ C$ ⁶⁾
Isolation capacitance	C_{IO}	<2	pF	$f = 1$ MHz ^{6) 7)}

1) Creepage and clearance requirements depend on the application and related end-equipment isolation standards. Care should be taken to keep the required creepage and clearance value on printed circuit board level.

2) See UL1577 certificate n. E311313.

3) Safety certification planned. The IEC 60747-17 and its German equivalent VDE 0884-17 is the successor of the component standard VDE 0884-11, which will expire in 2023.

4) The partial discharge voltage $V_{PD(m)}$ applied during productive tests is greater ($2110 V_{pk} > 1.65 \times V_{IORM}$) to include the F_4 factor (1.1) that takes into account the maximum deviation of the mains supply voltage from its nominal value as specified by the end-equipment standards IEC 60664-1, IEC 62368-1 ($V_{PD(m)} = F_1 \times F_2 \times F_4 \times V_{IORM} = 1.5 \times F_4 \times V_{IORM}$).

5) The surge test is performed in insulation oil to determine the intrinsic surge immunity of the insulation barrier.

6) The parameters apply to the product configured as a two terminals device with all terminals on side 1 connected together and all terminals on side 2 connected together.

7) Parameter not tested in production.

4 Thermal and electrical characteristics

4.8.2 Safety-limiting values

This digital isolator is suitable for the rated insulation only within the safety-limiting values. Compliance with these safety-limiting values must be ensured by means of suitable protective circuits.

Parameter	Symbol	Value	Unit	Note or condition
Maximum ambient safety temperature	T_S	150	°C	
Safety power dissipation	P_S	1.10	W	$R_{thJA} = 113 \text{ K/W}, T_A = 25^\circ\text{C}, T_J = 150^\circ\text{C}$
Safety supply current	$I_{S,TOT}$	220	mA	$R_{thJA} = 113 \text{ K/W}, T_A = 25^\circ\text{C}, T_J = 150^\circ\text{C}, V_{DDX} = 5.0 \text{ V}$

4.8.2.1 Thermal derating curve

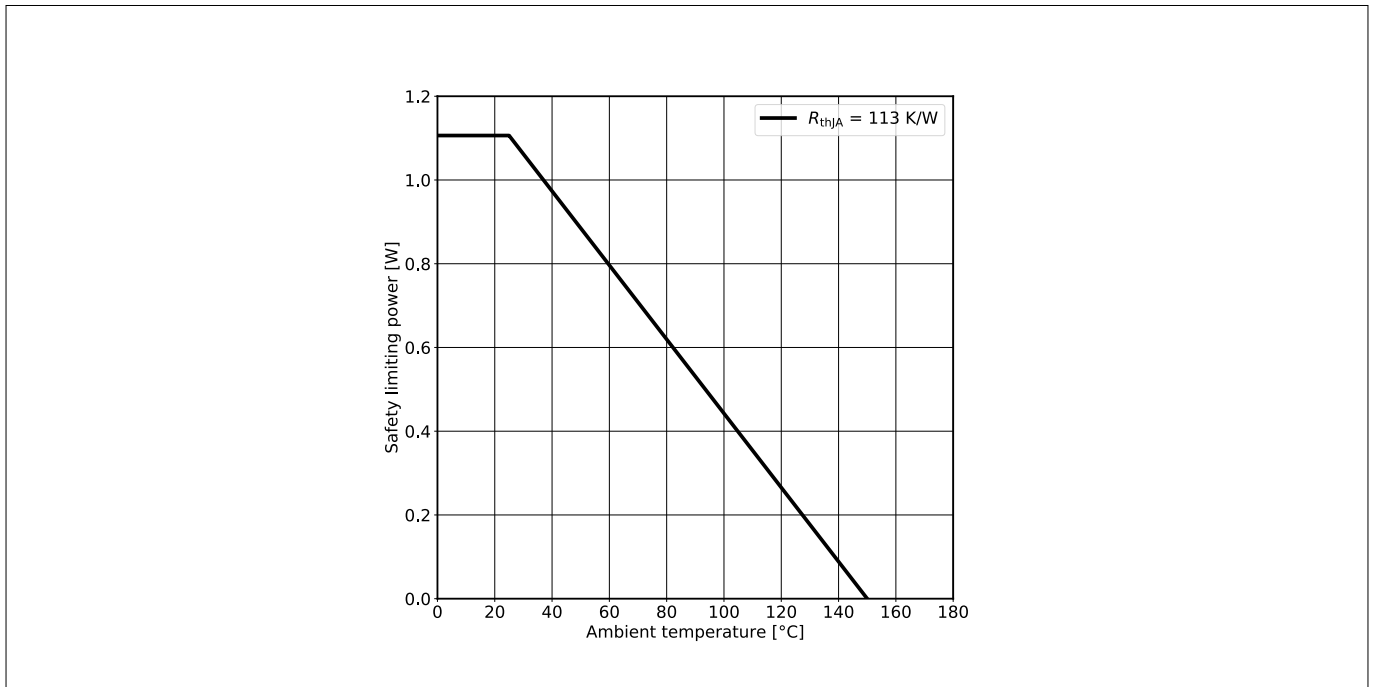


Figure 22 Thermal derating curve

5 Application and Implementation

5.1 Detailed Description

ISOFACE™ 2DIBx40xF is a family of high-performance digital isolators enabling robust data transmission over a SiO₂ isolation barrier. These devices have a very wide operating supply voltage range of 2.7 V to 6.5 V on both sides of the isolation barrier. Each side of the digital isolator can be independently supplied with any voltage between 2.7 V and 6.5 V irrespective of the supply voltage on the other side. For example, side 1 (V_{DD1}) of the digital isolator could be supplied with 3.3 V and side 2 (V_{DD2}) with 5 V. Therefore, these digital isolators in addition to providing safety isolation also act as logic-level translators in applications that are powered by different supply voltages.

The ISOFACE™ 2DIBx40xF family features variable CMOS input configurations for high noise immunity and signal integrity ensuring robust signal transmission in noisy environments. Only two external bypass capacitors (one on each side of the digital isolators) of 0.1 μ F are needed for proper functionality, thereby facilitating high-density PCB designs compared to optical isolators. An internal glitch filter on the inputs of each channel filters any signals below 10 ns, thereby preventing unwanted noise from corrupting the original data. With 3000 V_{rms} isolation voltage (V_{ISO} according to UL1577), ISOFACE™ 2DIBx40xF digital isolators are highly suitable for isolating gate-drive PWM signals from microcontrollers or isolating a bi-directional communication interface such as Controller Area Network (CAN) or Universal Asynchronous Receiver Transmitter (UART).

5 Application and Implementation

5.2 Application examples

5.2.1 Isolating gate drive control signals

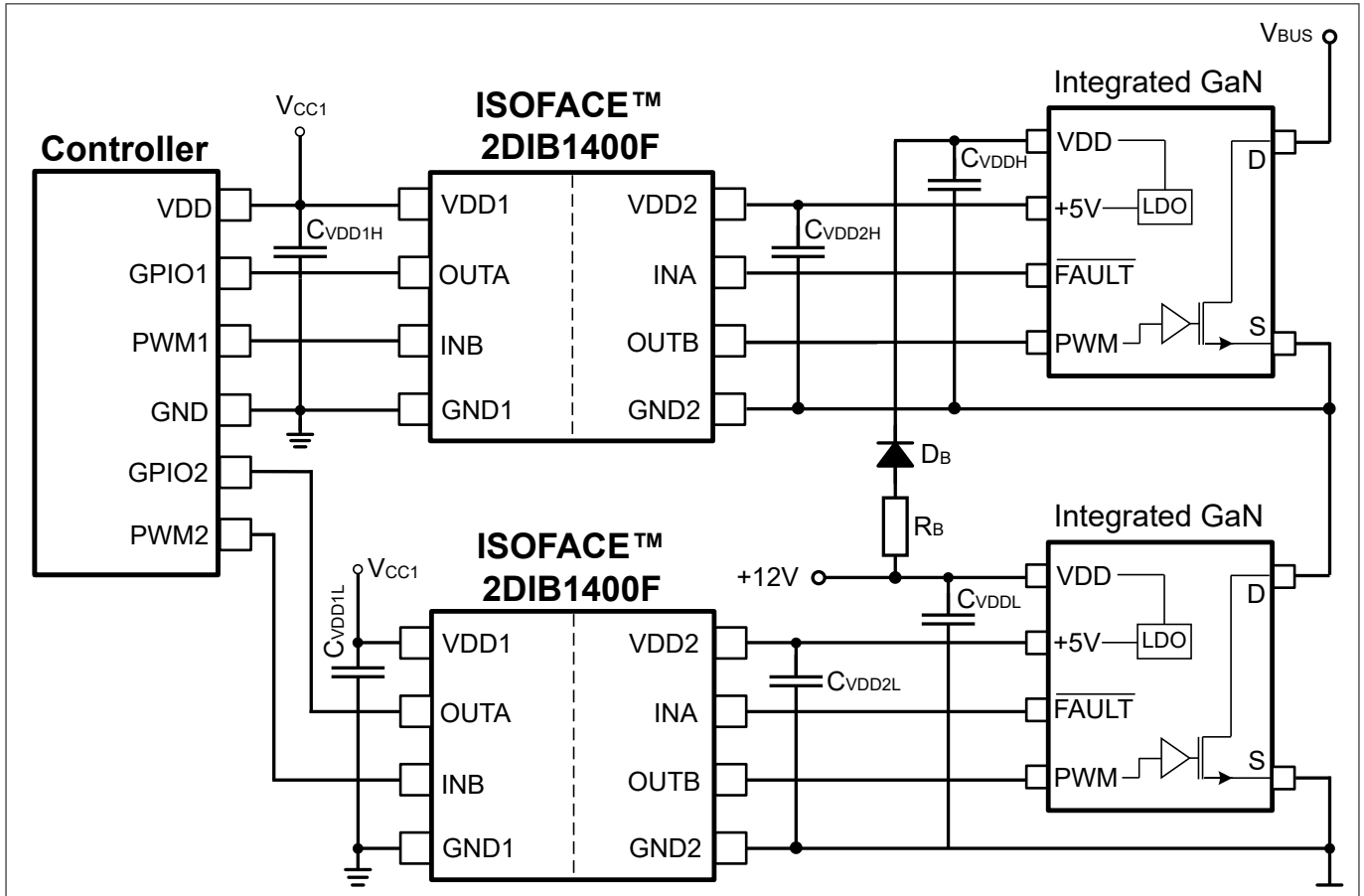


Figure 23 Typical application - Functional isolation for high-side GaN switch with integrated power stage

Figure 23 shows an example application where the ISOFACE™ 2DIB1400F is used to provide functional isolation for the gate drive signal of high-side switch in a typical half-bridge configuration. In this example, Gallium Nitride (GaN) switches with integrated drivers are shown. The controller is on side 1 of the digital isolator and the side 2 of the digital isolator is connected to the integrated GaN power stage. A digital isolator having 1 forward and 1 reverse channel (1+1) with default low output state option is selected for this application to isolate both the PWM signal from the controller to the integrated GaN switch and the fault signal from integrated GaN switch back to the controller. A low default output state ensures safety by keeping the switch in "off" state when the side 1 power supply is faulty.

The high switching frequency operation supported by GaN devices results in very fast switching transients that could pass through the isolation barrier and appear as noise on the input channel, resulting in the switch accidentally turning on if it is not protected properly. With excellent common-mode transient immunity (CMTI) of 100 kV/μs (min), the ISOFACE™ 2DIB1400F prevents the switching transients from crossing the isolation barrier and ensures safe high-density power supply applications using wide-band gap semiconductor switches. With a very low propagation delay spread (of -5/+6 ns), the ISOFACE™ 2DIB1400F family of digital isolators enables efficient switched-mode power supply designs.

5 Application and Implementation

5.2.2 Isolating communication interfaces

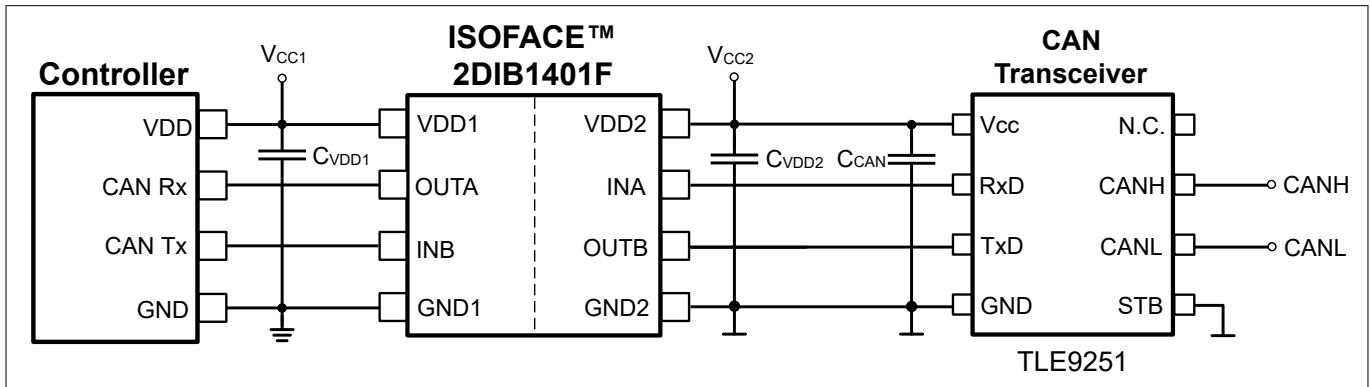


Figure 24 Typical application - Functional isolation of Controller Area Network (CAN) communication

Figure 24 shows an example application where the ISOFACE™ 2DIB1401F is used to isolate a CAN communication interface. The digital isolator is used to isolate the TxD and RxD signals from the microcontroller to a high speed CAN FD transceiver like TLE 9251. Side 1 of the digital isolator is powered from the same supply (V_{CC1}) as the microcontroller with either 3.3 V or 5 V, irrespective of the supply voltage on side 2 (V_{CC2}), which is powered with the same supply as the CAN transceiver. With a maximum data rate of 40 Mbps and a very low pulse-width distortion (< 3 ns), the ISOFACE™ 2DIB1401F digital isolator ensures reliable communication in isolating high speed CAN FD transceivers. The variant with high as default output state is selected for this application since the default state of the CAN communication bus is logical high.

6 Package dimensions

6 Package dimensions

The package dimensions of dual-channel digital isolator are provided.

Package PG-DSO-8 narrow-body 150-mil

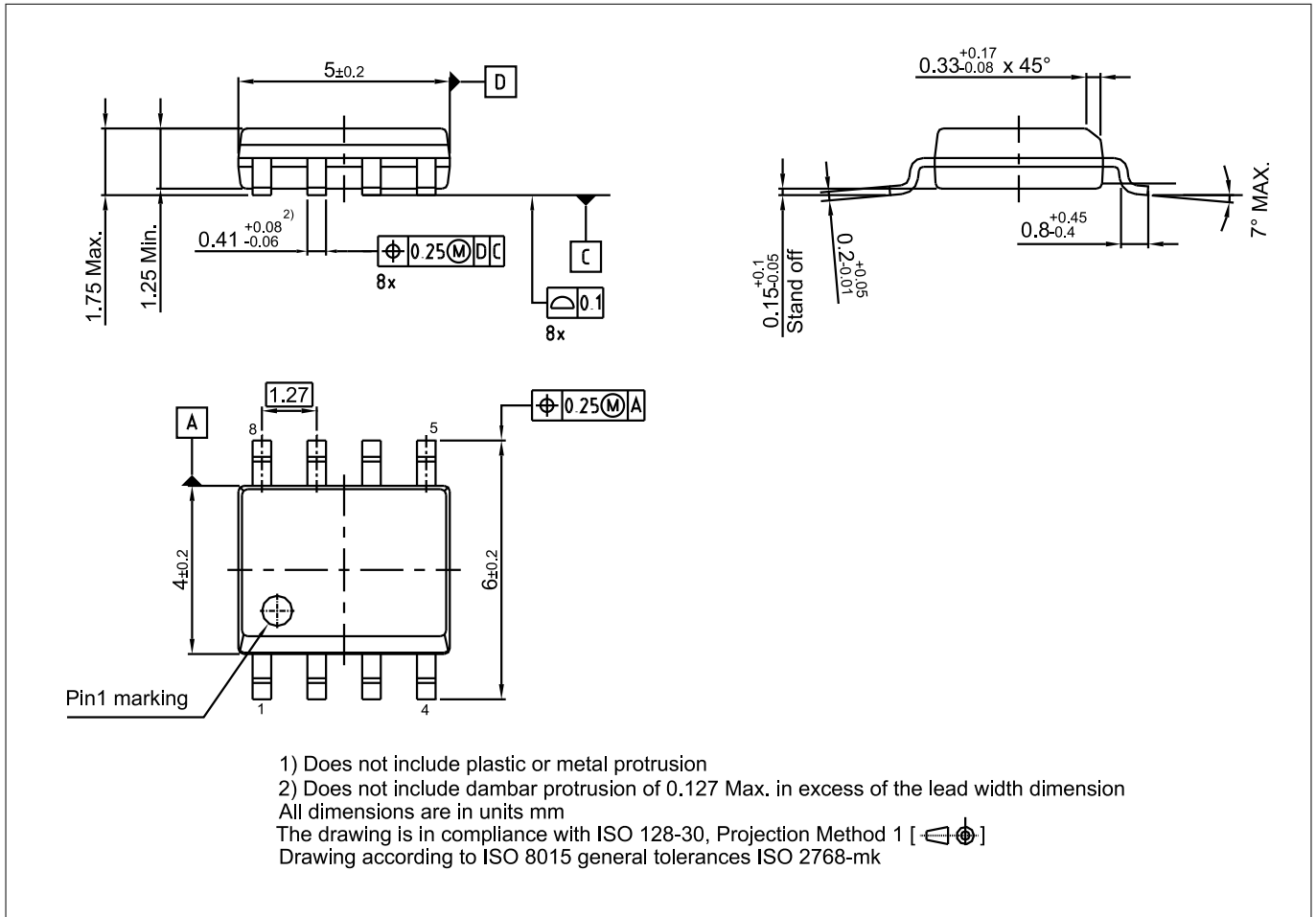


Figure 25 PG-DSO-8 narrow-body 150-mil outline

6 Package dimensions

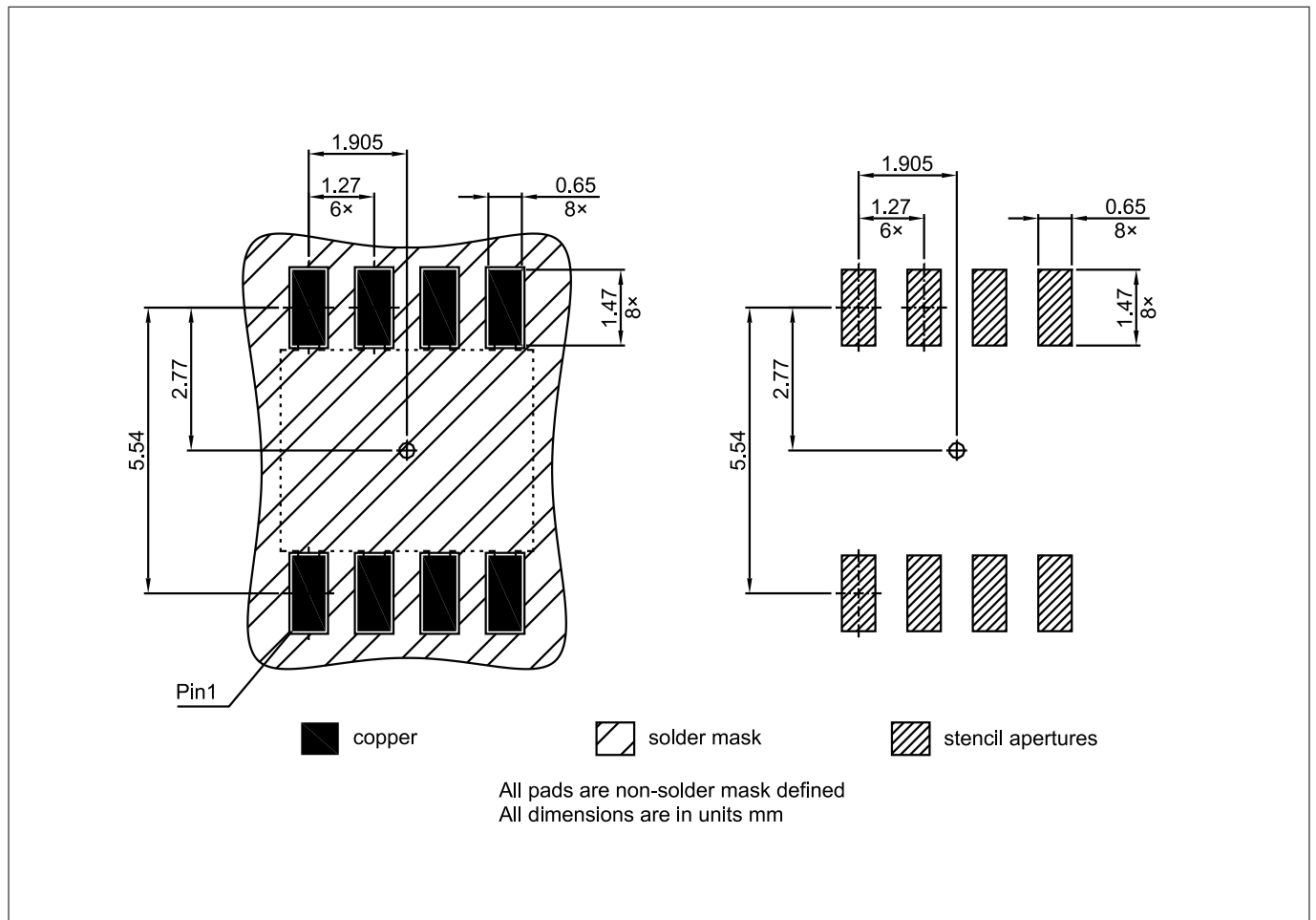


Figure 26 PG-DSO-8 narrow-body 150-mil footprint

6 Package dimensions

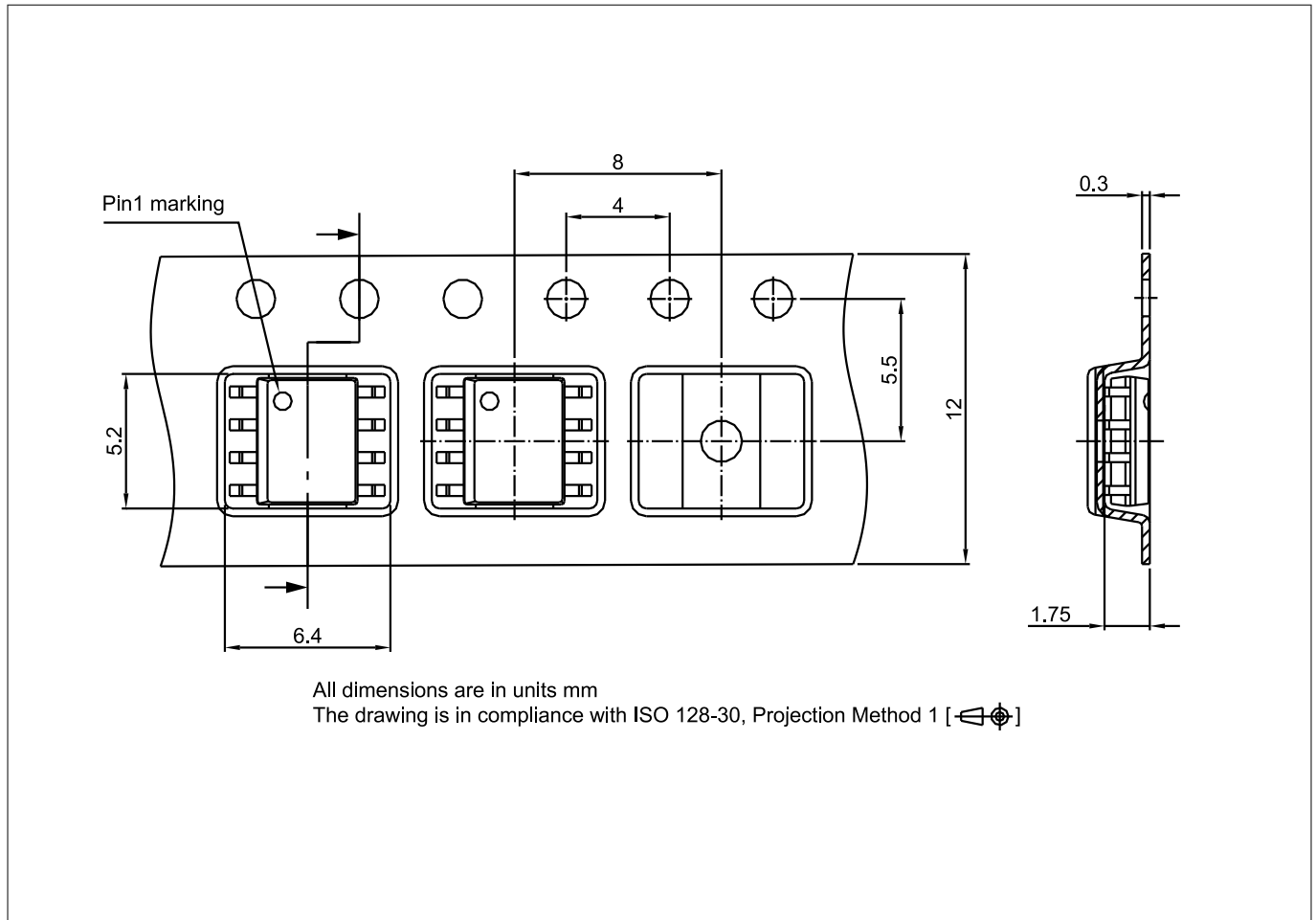


Figure 27 PG-DSO-8 narrow-body 150-mil packing

Green product (RoHS-compliant)

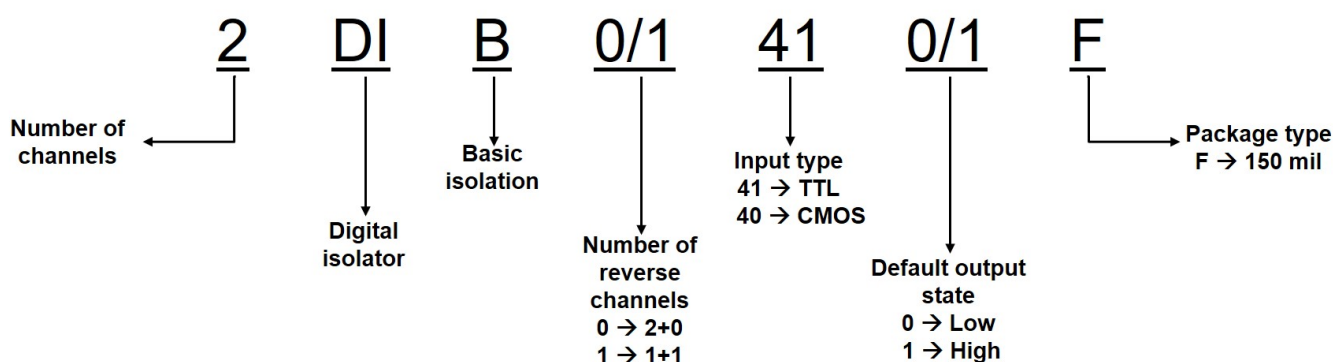
To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations, the device is available as a green product. Green products are RoHS-compliant (i.e. they have Pb-free finish on leads and are suitable for Pb-free soldering according to IPC/JEDEC J-STD-020).

Further information on packages: <https://www.infineon.com/packages>

7 Ordering guide

7 Ordering guide

Orderable part number (OPN)	Part number	Channel configuration	Default output state	Input thresholds	Package marking
2DIB0400FXUMA1	2DIB0400F	2 forward 0 reverse (2+0)	Low	Variable (CMOS)	2B0400A
2DIB0401FXUMA1	2DIB0401F		High		2B0401A
2DIB1400FXUMA1	2DIB1400F	1 forward 1 reverse (1+1)	Low		2B1400A
2DIB1401FXUMA1	2DIB1401F		High		2B1401A



8 Revision history

8 Revision history

Revision number	Major changes since previous revision
1.0, 2023-03-22	Datasheet initial release

Trademarks

All referenced product or service names and trademarks are the property of their respective owners.

Edition 2023-03-22

Published by

Infineon Technologies AG

81726 Munich, Germany

© 2023 Infineon Technologies AG

All Rights Reserved.

Do you have a question about any aspect of this document?

Email: erratum@infineon.com

Document reference

IFX-wro1669815735528

Important notice

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffheitsgarantie").

With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

In addition, any information given in this document is subject to customer's compliance with its obligations stated in this document and any applicable legal requirements, norms and standards concerning customer's products and any use of the product of Infineon Technologies in customer's applications.

The data contained in this document is exclusively intended for technically trained staff. It is the responsibility of customer's technical departments to evaluate the suitability of the product for the intended application and the completeness of the product information given in this document with respect to such application.

Warnings

Due to technical requirements products may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies office.

Except as otherwise explicitly approved by Infineon Technologies in a written document signed by authorized representatives of Infineon Technologies, Infineon Technologies' products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.